NXP Semiconductors

Data Sheet: Technical Data

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MCIMX6G1AVM05AA MCIMX6G1AVM05AB MCIMX6G1AVM07AA MCIMX6G1AVM07AB MCIMX6G2AVM05AA MCIMX6G2AVM05AB MCIMX6G2AVM07AA

i.MX 6UltraLite Automotive Applications Processors

Package Information Plastic Package BGA 14 x 14 mm, 0.8 mm pitch

Ordering Information

1 i.MX 6UltraLite introduction

The i.MX 6UltraLite is a high performance, ultra efficient processor family featuring NXP's advanced implementation of the single ARM Cortex®-A7 core, which operates at speeds up to 696 MHz. The i.MX 6UltraLite includes an integrated power management module that reduces the complexity of the external power supply and simplifies the power sequencing. Each processor in this family provides various memory interfaces, including LPDDR2, DDR3, DDR3L, Raw and Managed NAND flash, NOR flash, eMMC, Quad SPI, and a wide range of other interfaces for connecting peripherals, such as WLAN, Bluetooth™, GPS, displays, and camera sensors.

The i.MX 6UltraLite is specifically useful for automotive applications such as:

- Telematics
- Human Machine Interfaces (HMI)

The features of the i.MX 6UltraLite processor include¹:

- Single-core ARM Cortex-A7—The single core A7 provides a cost-effective and power-efficient solution.
- Multilevel memory system—The multilevel memory system of each device is based on the L1 instruction and data caches, L2 cache, and internal and external memory. The device supports many types of external memory devices, including DDR3, low voltage DDR3, LPDDR2, NOR Flash, NAND Flash (MLC and SLC), OneNAND™, Quad SPI, and managed NAND, including eMMC up to rev 4.4/4.41/4.5.
- Smart speed technology—Power management implemented throughout the IC that enables multimedia features and peripherals to consume minimum power in both active and various low power modes.
- Dynamic voltage and frequency scaling—The processor improves the power efficiency by scaling the voltage and frequency to optimize performance.
- Multimedia powerhouse—Multimedia performance is enhanced by a multilevel cache system, NEON™ MPE (Media Processor Engine) co-processor, a programmable smart DMA (SDMA) controller, an asynchronous audio sample rate converter, and a Pixel processing pipeline (PXP) to support 2D image processing, including color-space conversion, scaling, alpha-blending, and rotation.
- Ethernet interfaces—10/100 Mbps Ethernet controllers.
- Human-machine interface—Support digital parallel display interface.
- Interface flexibility—Each processor supports connections to a variety of interfaces: High-speed USB on-the-go with PHY, multiple expansion card port (high-speed MMC/SDIO host and other), 12-bit ADC module, CAN port, smart card interface compatible with EMV Standard v4.3, and a variety of other popular interfaces (such as UART, I^2C , and I^2S serial audio).
- Automotive environment support—Each processor includes interfaces, such as CAN, three SAI audio interfaces, and an asynchronous sample rate converter for multichannel/multisource audio.
- Advanced security—The processor delivers hardware-enabled security features that enable secure e-commerce, digital rights management (DRM), information encryption, secure boot, and secure software downloads. The security features are discussed in detail in the *i.MX 6UltraLite Security Reference Manual* (IMX6ULSRM).
- Integrated power management—The processor integrates linear regulators and internally generate voltage levels for different domains. This significantly simplifies system power management structure.

For a comprehensive list of the i.MX 6UltraLite features, see [Section 1.2, "Features""](#page-5-0).

^{1.} The actual feature set depends on the part numbers as described in the [Table 1](#page-2-0) and [Table 2.](#page-3-0)

1.1 Ordering information

[Table 1](#page-2-0) provides examples of orderable part numbers covered by this data sheet. The automotive parts in this subset of the i.MX 6UltraLite derivatives are single core devices offered in a 14x14 mm, 0.8 pitch BGA whose temperature range is -40 \degree C to 125 \degree C. Each of these devices have differences in characteristics or features according to the [Table 2](#page-3-0).

Part Number	Core Frequency	eFuse Bits	Ethernet Ports (10/100M)	CAN	ADC	CSI	LCD IF
MCIMX6G1AVM05AA	528 MHz	1024		1	1	No	No.
MCIMX6G1AVM05AB	528 MH _z	1024		1	1	No	No
MCIMX6G1AVM07AA	696 MHz	1024		1	1	No	No.
MCIMX6G1AVM07AB	696 MHz	1024		1	1	No	No.
MCIMX6G2AVM05AA	528 MHz	1536	2	2	$\overline{2}$	Yes	Yes
MCIMX6G2AVM05AB	528 MHz	1536	2	2	$\overline{2}$	Yes	Yes
MCIMX6G2AVM07AA	696 MHz	1536	2	$\overline{2}$	$\overline{2}$	Yes	Yes
MCIMX6G2AVM07AB	696 MHz	1536	2	2	$\overline{2}$	Yes	Yes

Table 1. Ordering Information

[Figure 1](#page-3-1) describes the part number nomenclature so that characteristics of a specific part number can be identified (for example, cores, frequency, temperature grade, fuse options, and silicon revision). The primary characteristic which describes which data sheet applies to a specific part is the temperature grade (junction) field.

• The i.MX 6UltraLite Automotive Applications Processors Data Sheet (IMX6ULAEC) covers parts listed with an "A (Automotive temp)"

Ensure to have the proper data sheet for specific part by verifying the temperature grade (junction) field and matching it to the proper data sheet. If there are any questions, visit the web page nxp.com/imx6series or contact an NXP representative for details.

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Figure 1. Part Number Nomenclature—i.MX 6UltraLite

[Table 2](#page-3-0) shows the detailed information about peripherals.

1 For detailed pin mux information, please refer to "Chapter 4 External Signals and Pin Multiplexing" of *i.MX 6UltraLite Reference Manual* (IMX6ULRM).

² Y stands for yes, NA stands for not available.

³ G0 and G3 are offered in automotive grade.

1.2 Features

The i.MX 6UltraLite processors are based on ARM Cortex-A7 MPCore™ Platform, which has the following features:

- Supports single ARM Cortex-A7 MPCore (with TrustZone) with:
	- 32 KBytes L1 Instruction Cache
	- 32 KBytes L1 Data Cache
	- Private Timer
	- Cortex-A7 NEON Media Processing Engine (MPE) Co-processor
- General Interrupt Controller (GIC) with 128 interrupts support
- Global Timer
- Snoop Control Unit (SCU)
- 128 KB unified I/D L2 cache
- Single Master AXI bus interface output of L2 cache
- Frequency of the core (including Neon and L1 cache), as per [Table 10, "Operating Ranges," on](#page-22-0) [page 23.](#page-22-0)

The SoC-level memory system consists of the following additional components:

- Boot ROM, including HAB (96 KB)
- Internal multimedia/shared, fast access RAM (OCRAM, 128 KB)
- Secure/non-secure RAM (32 KB)
- External memory interfaces: The i.MX 6UltraLite processors support handheld DRAM, NOR, and NAND Flash memory standards.
	- 16-bit LP-DDR2-800, 16-bit DDR3-800 and LV-DDR3-800
	- 8-bit NAND-Flash, including support for Raw MLC/SLC, 2 KB, 4 KB, and 8 KB page size, BA-NAND, PBA-NAND, LBA-NAND, OneNAND™ and others. BCH ECC up to 40 bits.
	- 16/8-bit NOR Flash. All EIMv2 pins are muxed on other interfaces.

Each i.MX 6UltraLite processor enables the following interfaces to external devices (some of them are muxed and not available simultaneously):

- Displays:
	- One parallel display port supports max 85 MHz display clock and up to WXGA (1366 x 768) at 60 Hz
	- Support 24-bit, 18-bit, 16-bit, and 8-bit parallel display
- Camera sensors¹:
	- One parallel camera port, up to 24 bit and 148.5 MHz pixel clock
	- Support 24-bit, 16-bit, 10-bit, and 8-bit input
	- Support BT.656 interface
- **Expansion cards:**
	- Two MMC/SD/SDIO card ports all supporting:
		- 1-bit or 4-bit transfer mode specifications for SD and SDIO cards up to UHS-I SDR-104 mode (104 MB/s max)
		- 1-bit, 4-bit, or 8-bit transfer mode specifications for MMC cards up to 52 MHz in both SDR and DDR modes (104 MB/s max)
		- 4-bit or 8-bit transfer mode specifications for eMMC chips up to 200 MHz in HS200 mode (200 MB/s max)
- USB:
	- Two high speed (HS) USB 2.0 OTG (Up to 480 Mbps) with integrated HS USB Phy
- Miscellaneous IPs and interfaces:
	- Three SAI supporting up to three I2S
	- Sony Philips Digital Interconnect Format (SPDIF), Rx and Tx
	- Eight UARTs, up to 5.0 Mbps each:
		- Providing RS232 interface
		- Supporting 9-bit RS485 multidrop mode
		- Support RTS/CTS for hardware flow control
	- Four enhanced CSPI (eCSPI)
- 1. G2 and G3 only

- Four I^2C
- Two 10/100M Ethernet Controller (IEEE1588 compliant)
- Eight Pulse Width Modulators (PWM)
- System JTAG Controller (SJC)
- GPIO with interrupt capabilities
- 8x8 Key Pad Port (KPP)
- One Quad SPI
- Two Flexible Controller Area Network (FlexCAN)
- Three Watchdog timers (WDOG)
- Two 12-bit Analog to Digital Converters (ADC) with up to 10 input channels in total
- Touch Screen Controller (TSC)

The i.MX 6UltraLite processors integrate advanced power management unit and controllers:

- Provide PMU, including LDO supplies, for on-chip resources
- Use Temperature Sensor for monitoring the die temperature
- Use Voltage Sensor for monitoring the die voltage
- Support DVFS techniques for low power modes
- Use SW State Retention and Power Gating for ARM and NEON
- Support various levels of system power modes
- Use flexible clock gating control scheme
- Two smart card interfaces compatible with EVM Standard 4.3

The i.MX 6UltraLite processors use dedicated hardware accelerators to meet the targeted multimedia performance. The use of hardware accelerators is a key factor in obtaining high performance at low power consumption, while having the CPU core relatively free for performing other tasks.

The i.MX 6UltraLite processors incorporate the following hardware accelerators:

- PXP—Pixel Processing Pipeline for imagine resize, rotation, overlay and $CSC¹$. Off loading key pixel processing operations are required to support the LCD display applications.
- ASRC—Asynchronous Sample Rate Converter

Security functions are enabled and accelerated by the following hardware:

- ARM TrustZone including the TZ architecture (separation of interrupts, memory mapping, etc.)
- SJC—System JTAG Controller. Protecting JTAG from debug port attacks by regulating or blocking the access to the system debug features.
- CAAM—Cryptographic Acceleration and Assurance Module, containing cryptographic and hash engines, 32 KB secure RAM, and True and Pseudo Random Number Generator (NIST certified).
- SNVS—Secure Non-Volatile Storage, including Secure Real Time Clock.
- CSU—Central Security Unit. CSU is configured during boot and by eFUSEs and determine the security level operation mode as well as the TZ policy.

1. G2 and G3 only

• A-HAB—Advanced High Assurance Boot—HABv4 with the new embedded enhancements: SHA-256, 2048-bit RSA key, version control mechanism, warm boot, CSU, and TZ initialization.

NOTE

The actual feature set depends on the part numbers as described in [Table 1](#page-2-0) and [Table 2.](#page-3-0) Functions such as display and camera interfaces, connectivity interfaces, and security features are not offered on all derivatives.

Architectural overview

2 Architectural overview

The following subsections provide an architectural overview of the i.MX 6UltraLite processor system.

2.1 Block diagram

[Figure 2](#page-9-2) shows the functional modules in the i.MX 6UltraLite processor system.

Figure 2. i.MX 6UltraLite System Block Diagram¹

^{1.} Some modules shown in this block diagram are not offered on all derivatives. See [Table 2](#page-3-0) for exceptions.

The i.MX 6UltraLite processors contain a variety of digital and analog modules. [Table 3](#page-10-1) describes these modules in alphabetical order.¹

Block Mnemonic	Block Name	Subsystem	Brief Description
ADC1 ADC ₂	Analog to Digital Converter		The ADC is a 12-bit general purpose analog to digital converter.
ARM	ARM Platform	ARM	The ARM Core Platform includes 1x Cortex-A7 core. It also includes associated sub-blocks, such as the Level 2 Cache Controller, SCU (Snoop Control Unit), GIC (General Interrupt Controller), private timers, watchdog, and CoreSight debug modules.
ASRC	Asynchronous Sample Rate Converter	Multimedia Peripherals	The Asynchronous Sample Rate Converter (ASRC) converts the sampling rate of a signal associated to an input clock into a signal associated to a different output clock. The ASRC supports concurrent sample rate conversion of up to 10 channels of about -120dB THD+N. The sample rate conversion of each channel is associated to a pair of incoming and outgoing sampling rates. The ASRC supports up to three sampling rate pairs.
BCH	Binary-BCH ECC Processor	System Control Peripherals	The BCH module provides up to 40-bit ECC for NAND Flash controller (GPMI)
CAAM	Cryptographic accelerator and assurance module	Security	CAAM is a cryptographic accelerator and assurance module. CAAM implements several encryption and hashing functions, a run-time integrity checker, and a Pseudo Random Number Generator (PRNG). The pseudo random number generator is certified by Cryptographic Algorithm Validation Program (CAVP) of National Institute of Standards and Technology (NIST). Its deterministic random bit generator (DRBG) validation number is 94 and its SHS validation number is 1455. CAAM also implements a Secure Memory mechanism. In i.MX 6UltraLite processors, the security memory provided is 32 KB.
CCM GPC SRC	Clock Control Module, General Power Controller, System Reset Controller	Clocks, Resets, and Power Control	These modules are responsible for clock and reset distribution in the system, and also for the system power management.
CSI	Parallel CSI	Multimedia Peripherals	The CSI IP provides parallel CSI standard camera interface port. The CSI parallel data ports are up to 24 bits. It is designed to support 24-bit RGB888/YUV444, CCIR656 video interface, 8-bit YCbCr, YUV or RGB, and 8-bit/10-bit/16-bit Bayer data input.

Table 3. i.MX 6UltraLite Modules List

1. Note that some modules listed in this table are not offered on all derivatives. See [Table 2](#page-3-0) for exceptions.

Table 3. i.MX 6UltraLite Modules List (continued)

Table 3. i.MX 6UltraLite Modules List (continued)

Table 3. i.MX 6UltraLite Modules List (continued)

3.1 Special signal considerations

[Table 4](#page-16-1) lists special signal considerations for the i.MX 6UltraLite processors. The signal names are listed in alphabetical order.

The package contact assignments can be found in [Section 6, "Package information and contact](#page-102-0) [assignments".](#page-102-0)" Signal descriptions are provided in the *i.MX 6UltraLite Reference Manual* (IMX6ULRM).

Table 4. Special Signal Considerations

Table 5. JTAG Controller Interface Summary

Table 5. JTAG Controller Interface Summary (continued)

3.2 Recommended connections for unused analog interfaces

[Table 6](#page-18-1) shows the recommended connections for unused analog interfaces.

Table 6. Recommended Connections for Unused Analog Interfaces

4 Electrical characteristics

This section provides the device and module-level electrical characteristics for the i.MX 6UltraLite processors.

4.1 Chip-Level conditions

This section provides the device-level electrical characteristics for the IC. See [Table 7](#page-19-4) for a quick reference to the individual tables and sections.

For these characteristics	Topic appears
Absolute maximum ratings	on page 20
Thermal resistance	on page 21
Operating ranges	on page 22
External clock sources	on page 24
Maximum supply currents	on page 25
Low power mode supply currents	on page 27
USB PHY current consumption	on page 28

Table 7. i.MX 6UltraLite Chip-Level Conditions

4.1.1 Absolute maximum ratings

CAUTION

Stress beyond those listed under [Table 8](#page-19-3) may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

[Table 8](#page-19-3) shows the absolute maximum operating ratings.

Table 8. Absolute Maximum Ratings

 $\frac{1}{1}$ The absolute maximum voltage includes an allowance for 400 mV of overshoot on the IO pins. Per JEDEC standards, the allowed signal overshoot must be derated if NVCC_DRAM exceeds 1.575 V.

² OVDD is the I/O supply voltage.

4.1.2 Thermal resistance

4.1.2.1 14x14 MM (VM) package thermal resistance

[Table 9](#page-20-3) displays the 14x14 MM (VM) package thermal resistance data.

Table 9. 14x14 MM (VM) Thermal Resistance Data1

Rating	Test Conditions	Symbol	Value	Unit	Notes
Junction to Ambient Natural convection	Single-layer board (1s)	R_{θ JA	58.4	°C/W	2,3
Junction to Ambient Natural convection	Four-layer board (2s2p)	R_{θ JA	37.6	°C/W	3,3,4
Junction to Ambient (@200 ft/min)	Single layer board (1s)	$R_{\theta JMA}$	48.6	°C/W	2,4
Junction to Ambient (@200 ft/min)	Four layer board (2s2p)	$R_{\theta JMA}$	32.9	°C/W	2,4

Table 9. 14x14 MM (VM) Thermal Resistance Data1

 $¹$ As per JEDEC JESD51-2 the intent of (thermal resistance) measurement is solely for a thermal performance comparison of</sup> one package to another in a standardized environment. This methodology is not meant to and will not predict the performance of a package in an application-specific environment.

² Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.

- ³ Per SEMI G38-87 and JEDEC JESD51-2 with the single layer board horizontal.
- ⁴ Per JEDEC JESD51-6 with the board horizontal.
- ⁵ Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- 6 Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
- 7 Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.
- ⁸ Thermal characterization parameter indicating the temperature difference between package bottom center and the junction temperature per JEDEC JESD51-12. When Greek letters are not available, the thermal characterization parameter is written as Psi-JB

4.1.3 Operating ranges

[Table 10](#page-22-0) provides the operating ranges of the i.MX 6UltraLite processors. For details on the chip's power structure, see the "Power Management Unit (PMU)" chapter of the *i.MX 6UltraLite Reference Manual* (IMX6ULRM).

Table 10. Operating Ranges

Table 10. Operating Ranges (continued)

Applying the maximum voltage results in maximum power consumption and heat generation. NXP recommends a voltage set point = $(V_{min}$ + the supply tolerance). This result in an optimized power/speed ratio.

² In setting VDD_HIGH_IN voltage, refer to the Errata ERR010690 (SNVS_LP Registers Reset Issue).

³ In setting VDD_SNVS_IN voltage with regards to Charging Currents and RTC, refer to the *i.MX 6UltraLite Hardware Development Guide* (IMX6ULHDG).

[Table 11](#page-23-1) shows on-chip LDO regulators that can supply on-chip loads.

Table 11. On-Chip LDOs1 and their On-Chip Loads

 1 On-chip LDOs are designed to supply i.MX6UltraLite loads and must not be used to supply external loads.

4.1.4 External clock sources

Each i.MX 6UltraLite processor has two external input system clocks: a low frequency (RTC_XTALI) and a high frequency (XTALI).

The RTC XTALI is used for low-frequency functions. It supplies the clock for wake-up circuit, power-down real time clock operation, and slow system and watch-dog counters. The clock input can be connected to either external oscillator or a crystal using internal oscillator amplifier. Additionally, there is an internal ring oscillator, which can be used instead of the RTC_XTALI if accuracy is not important.

The system clock input XTALI is used to generate the main system clock. It supplies the PLLs and other peripherals. The system clock input can be connected to either external oscillator or a crystal using internal oscillator amplifier.

[Table 12](#page-24-2) shows the interface frequency requirements.

 1 External oscillator or a crystal with internal oscillator amplifier.

² The required frequency stability of this clock source is application dependent. For recommendations, see the Hardware Development Guide for *i.MX 6UltraLite Applications Processors* (IMX6ULHDG).

³ Recommended nominal frequency 32.768 kHz.

⁴ External oscillator or a fundamental frequency crystal with internal oscillator amplifier.

The typical values shown in [Table 12](#page-24-2) are required for use with NXP BSPs to ensure precise time keeping and USB operation. For RTC_XTALI operation, two clock sources are available.

- On-chip 40 kHz ring oscillator—this clock source has the following characteristics:
	- Approximately 25 µA more Idd than crystal oscillator
	- Approximately $\pm 50\%$ tolerance
	- No external component required
	- Starts up quicker than 32 kHz crystal oscillator
- External crystal oscillator with on-chip support circuit:
	- At power up, ring oscillator is utilized. After crystal oscillator is stable, the clock circuit switches over to the crystal oscillator automatically.
	- Higher accuracy than ring oscillator
	- If no external crystal is present, then the ring oscillator is utilized

The decision of choosing a clock source should be taken based on real-time clock use and precision time-out.

4.1.5 Maximum supply currents

The data shown in [Table 13](#page-25-0) represent a use case designed specifically to show the maximum current consumption possible. All cores are running at the defined maximum frequency and are limited to L1 cache accesses only to ensure no pipeline stalls. Although a valid condition, it would have a very limited practical use case, if at all, and be limited to an extremely low duty cycle unless the intention was to specifically show the worst case power consumption.

See the i.MX 6UltraLite Power Consumption Measurement Application Note (AN5170) for more details on typical power consumption under various use case definitions.

 $\frac{1}{1}$ The actual maximum current drawn from VDD_HIGH_IN will be as shown plus any additional current drawn from the VDD_HIGH_CAP outputs, depending upon actual application configuration (for example, NVCC_DRAM_2P5 supplies).

 2 The maximum VDD_SNVS_IN current may be higher depending on specific operating configurations, such as BOOT_MODE[1:0] not equal to 00, or use of the Tamper feature. During initial power on, VDD_SNVS_IN can draw up to 1 mA, if available. VDD_SNVS_CAP charge time will increase if less than 1 mA is available.

³ This is the maximum current per active USB physical interface.

⁴ The DRAM power consumption is dependent on several factors, such as external signal termination. DRAM power calculators are typically available from the memory vendors. They take in account factors, such as signal termination. See the *i.MX 6UltraLite Power Consumption Measurement Application Note (AN5170)* or examples of DRAM power consumption during specific use case scenarios.

```
5 General equation for estimated, maximum power consumption of an IO power supply:
Imax = N \times C \times V \times (0.5 \times F)Where:
N—Number of IO pins supplied by the power line
C—Equivalent external capacitive load
V—IO voltage
(0.5 xF)—Data change rate. Up to 0.5 of the clock rate (F)
In this equation, Imax is in Amps, C in Farads, V in Volts, and F in Hertz.
```
4.1.6 Low power mode supply currents

[Table 14](#page-26-1) shows the current core consumption (not including I/O) of i.MX 6UltraLite processors in selected low power modes.

Mode	Test Conditions	Supply	Typical ¹	Units
SYSTEM IDLE: LDO Enabled	• LDO ARM and LDO SOC are set to 1.15 V	VDD SOC IN (1.275 V)	7.7	m _A
	• LDO 2P5 set to 2.5 V, LDO 1P1 set to 1.1 V • CPU in WFI, CPU clock gated	VDD HIGH IN (3.0 V)	10.5	
	• DDR is in self refresh • 24 MHz XTAL is ON	VDD_SNVS_IN (3.0 V)	0.06	
	• 528 PLL is active, other PLLS are power down • High-speed peripheral clock gated, but remain powered	Total	41.5	mW
SYSTEM IDLE:	• LDO ARM and LDO SOC are set to bypass	VDD_SOC_IN (1.15 V)	7.5	mA
LDO Bypassed	mode • LDO 2P5 set to 2.5 V, LDO 1P1 set to 1.1 V	VDD_HIGH_IN (3.0 V)	9.5	
	• CPU in WFI, CPU clock gated • DDR is in self refresh	VDD_SNVS_IN (3.0 V)	0.06	
	• 24 MHz XTAL is ON • 528 PLL is active, other PLLs are power down • High-speed peripheral clock gated, but remain powered	Total	37.3	mW
LOW POWER IDLE:	• LDO_SOC is set to 1.15 V, LDO_ARM is in PG	VDD_SOC_IN (1.275 V)	3.2	mA
LDO Enabled	mode • LDO 2P5 and LDO 1P1 are set to weak mode	VDD_HIGH_IN (3.0 V)	1.5	
	• CPU in power gate mode • DDR is in self refresh	VDD_SNVS_IN (3.0 V)	0.05	
	• All PLLs are power down • 24 MHz XTAL is off, 24 MHz RCOSC used as clock source • High-speed peripheral are powered off	Total	8.7	mW
LOW POWER IDLE:	• LDO SOC is in bypass mode, LDO ARM is in PG	VDD_SOC_IN (1.15 V)	2.8	mA
LDO Bypassed	mode • LDO-2P5 and LDO 1P1 are set to weak mode	VDD_HIGH_IN (3.0 V)	0.4	
	• CPU in power gate mode • DDR is in self refresh	VDD_SNVS_IN (3.0 V)	0.05	
	• All PLLs are power down • 24 MHz XTAL is off, 24 MHz RCOSC used as clock source • High-speed peripheral are powered off	Total	4.57	mW

Table 14. Low Power Mode Current and Power Consumption

SUSPEND	LDO SOC is in bypass mode, LDO ARM is in PG \bullet mode • LDO 2P5 and LDO 1P1 are shut off • CPU in power gate mode • DDR is in self refresh • All PLLs are power down • 24 MHz XTAL is off, 24 MHz RCOSC is off • All clocks are shut off, except 32 kHz RTC High-speed peripheral are powered off	VDD SOC IN $(0.9 V)$	0.44	mA
(DSM)		VDD HIGH IN (3.0 V)	0.03	
		VDD SNVS IN (3.0 V)	0.03	
		Total	0.58	mW
SNVS (RTC)	• All SOC digital logic, analog module are shut off • 32 kHz RTC is alive Tamper detection circuit remains active	VDD SOC IN (0 V)	Ω	mA
		VDD HIGH IN (0 V)	Ω	
		VDD SNVS_IN (3.0 V)	0.02	
		Total	0.06	mW

Table 14. Low Power Mode Current and Power Consumption (continued)

 1 Typical process material in fab

4.1.7 USB PHY current consumption

4.1.7.1 Power down mode

In power down mode, everything is powered down, including the USB VBUS valid detectors in typical condition. [Table 15](#page-27-2) shows the USB interface current consumption in power down mode.

Table 15. USB PHY Current Consumption in Power Down Mode

	VDD_USB_CAP (3.0 V)	VDD_HIGH_CAP (2.5 V)	$NVCC$ PLL $(1.1 V)$
l Current	$5.1 \mu A$	1.7 µA	$< 0.5 \mu A$

NOTE

The currents on the VDD_HIGH_CAP and VDD_USB_CAP were identified to be the voltage divider circuits in the USB-specific level shifters.

4.2 Power supplies requirements and restrictions

The system design must comply with power-up sequence, power-down sequence, and steady state guidelines as described in this section to guarantee the reliable operation of the device. Any deviation from these sequences may result in the following situations:

- Excessive current during power-up phase
- Prevention of the device from booting
- Irreversible damage to the processor (worst-case scenario)

4.2.1 Power-Up sequence

The below restrictions must be followed:

- VDD SNVS IN supply must be turned on before any other power supply or be connected (shorted) with VDD_HIGH_IN supply.
- If a coin cell is used to power VDD_SNVS_IN, then ensure that it is connected before any other supply is switched on.
- VDD HIGH IN should be turned on before VDD SOC IN.

NOTE

The POR B input (if used) must be immediately asserted at power-up and remain asserted until after the last power rail reaches its working voltage. In the absence of an external reset feeding the POR_B input, the internal POR module takes control. See the *i.MX 6UltraLite Reference Manual* (IMX6ULRM) for further details and to ensure that all necessary requirements are being met.

NOTE

Need to ensure that there is no back voltage (leakage) from any supply on the board towards the 3.3 V supply (for example, from the external components that use both the 1.8 V and 3.3 V supplies).

NOTE

USB OTG1 VBUS and USB OTG2 VBUS are not part of the power supply sequence and may be powered at any time.

4.2.2 Power-Down sequence

The following restrictions must be followed:

- VDD SNVS IN supply must be turned off after any other power supply or be connected (shorted) with VDD HIGH_IN supply.
- If a coin cell is used to power VDD_SNVS_IN, then ensure that it is removed after any other supply is switched off.

CAUTION

For power sequence control on VDD_HIGH_IN and VDD_SOC_IN, refer to the ERR010690 (SNVS_LP Registers Reset Issue).

4.2.3 Power supplies usage

All I/O pins should not be externally driven while the I/O power supply for the pin (NVCC_xxx) is OFF. This can cause internal latch-up and malfunctions due to reverse current flows. For information about I/O power supply of each pin, see "Power Rail" columns in pin list tables of [Section 6, "Package information](#page-102-0) [and contact assignments".](#page-102-0)"

4.3 Integrated LDO voltage regulator parameters

Various internal supplies can be powered ON from internal LDO voltage regulators. All the supply pins named * CAP must be connected to external capacitors. The onboard LDOs are intended for internal use only and should not be used to power any external circuitry. See the *i.MX 6UltraLite Reference Manual* (IMX6ULRM) for details on the power tree scheme.

NOTE

The * CAP signals should not be powered externally. These signals are intended for internal LDO operation only.

4.3.1 Digital regulators (LDO_ARM, LDO_SOC)

There are two digital LDO regulators ("Digital", because of the logic loads that they drive, not because of their construction). The advantages of the regulators are to reduce the input supply variation because of their input supply ripple rejection and their on-die trimming. This translates into more stable voltage for the on-chip logics.

These regulators have two basic modes:

- Power Gate. The regulation FET is switched fully off limiting the current draw from the supply. The analog part of the regulator is powered down here limiting the power consumption.
- Analog regulation mode. The regulation FET is controlled such that the output voltage of the regulator equals the programmed target voltage. The target voltage is fully programmable in 25 mV steps.

For additional information, see the *i.MX 6UltraLite Reference Manual* (IMX6ULRM).

4.3.2 Regulators for analog modules

4.3.2.1 LDO_1P1

The LDO 1P1 regulator implements a programmable linear-regulator function from VDD HIGH_IN (see [Table 10](#page-22-0) for minimum and maximum input requirements). Typical Programming Operating Range is 1.0 V to 1.2 V with the nominal default setting as 1.1 V. The LDO_1P1 supplies the USB Phy, and PLLs. A programmable brown-out detector is included in the regulator that can be used by the system to determine when the load capability of the regulator is being exceeded to take the necessary steps. Current-limiting can be enabled to allow for in-rush current requirements during start-up, if needed. Active-pull-down can also be enabled for systems requiring this feature.

For information on external capacitor requirements for this regulator, see the Hardware Development Guide for *i.MX 6UltraLite Applications Processors* (IMX6ULHDG).

For additional information, see the *i.MX 6UltraLite Reference Manual* (IMX6ULRM).

4.3.2.2 LDO_2P5

The LDO 2P5 module implements a programmable linear-regulator function from VDD HIGH_IN (see [Table 10](#page-22-0) for minimum and maximum input requirements). Typical Programming Operating Range is 2.25 V to 2.75 V with the nominal default setting as 2.5 V. LDO 2P5 supplies the DDR IOs, USB Phy, E-fuse module, and PLLs. A programmable brown-out detector is included in the regulator that can be used by the system to determine when the load capability of the regulator is being exceeded, to take the necessary steps. Current-limiting can be enabled to allow for in-rush current requirements during start-up, if needed. Active-pull-down can also be enabled for systems requiring this feature. An alternate self-biased low-precision weak-regulator is included that can be enabled for applications needing to keep the output voltage alive during low-power modes where the main regulator driver and its associated global bandgap reference module are disabled. The output of the weak-regulator is not programmable and is a function of the input supply as well as the load current. Typically, with a 3 V input supply the weak-regulator output is 2.525 V and its output impedance is approximately 40 Ω .

For information on external capacitor requirements for this regulator, see the *Hardware Development Guide for i.MX 6UltraLite Applications Processors* (IMX6ULHDG).

For additional information, see the *i.MX 6UltraLite Reference Manual* (IMX6ULRM).

4.3.2.3 LDO_USB

The LDO USB module implements a programmable linear-regulator function from the USB VUSB voltages (4.4 V–5.5 V) to produce a nominal 3.0 V output voltage. A programmable brown-out detector is included in the regulator that can be used by the system to determine when the load capability of the regulator is being exceeded, to take the necessary steps. This regulator has a built in power-mux that allows the user to select to run the regulator from either USB VBUS supply, when both are present. If only one of the USB VBUS voltages is present, then, the regulator automatically selects this supply. Current limit is also included to help the system meet in-rush current targets.

For information on external capacitor requirements for this regulator, see the Hardware Development Guide for *i.MX 6UltraLite Applications Processors* (IMX6ULHDG).

For additional information, see the *i.MX 6UltraLite Reference Manual* (IMX6ULRM).

4.4 PLL's electrical characteristics

4.4.1 Audio/Video PLL's electrical parameters

Table 16. Audio/Video PLL's Electrical Parameters

4.4.2 528 MHz PLL

Table 17. 528 MHz PLL's Electrical Parameters

4.4.3 Ethernet PLL

Table 18. Ethernet PLL's Electrical Parameters

4.4.4 480 MHz PLL

Table 19. 480 MHz PLL's Electrical Parameters

4.4.5 ARM PLL

Table 20. ARM PLL's Electrical Parameters

4.5 On-Chip oscillators

4.5.1 OSC24M

This block implements an amplifier that when combined with a suitable quartz crystal and external load capacitors implement an oscillator. The oscillator is powered from NVCC_PLL.

The system crystal oscillator consists of a Pierce-type structure running off the digital supply. A straight forward biased-inverter implementation is used.

4.5.2 OSC32K

This block implements an amplifier that when combined with a suitable quartz crystal and external load capacitors implement a low power oscillator. It also implements a power mux such that it can be powered from either a \sim 3 V backup battery (VDD_SNVS_IN) or VDD_HIGH_IN such as the oscillator consumes power from VDD HIGH IN when that supply is available and transitions to the backup battery when VDD_HIGH_IN is lost.

In addition, if the clock monitor determines that the OSC32K is not present, then the source of the 32 K will automatically switch to a crude internal ring oscillator. The frequency range of this block is approximately 10–45 kHz. It highly depends on the process, voltage, and temperature.

The OSC32k runs from VDD_SNVS_CAP supply, which comes from the

VDD HIGH IN/VDD SNVS IN. The target battery is a \sim 3 V coin cell. Proper choice of coin cell type is necessary for chosen VDD_HIGH_IN range. Appropriate series resistor (Rs) must be used when connecting the coin cell. Rs depends on the charge current limit that depends on the chosen coin cell. For example, for Panasonic ML621:

- Average Discharge Voltage is 2.5 V
- Maximum Charge Current is 0.6 mA

For a charge voltage of 3.2 V, $Rs = (3.2 - 2.5)/0.6$ m = 1.17 k.

	Min	Typ	Max	Comments
Fosc		32.768 KHz		This frequency is nominal and determined mainly by the crystal selected. 32.0 K would work as well.
Current consumption		$4 \mu A$		The 4 μ A is the consumption of the oscillator alone (OSC32k). Total supply consumption will depend on what the digital portion of the RTC consumes. The ring oscillator consumes 1 μ A when ring oscillator is inactive, 20 μ A when the ring oscillator is running. Another 1.5 μ A is drawn from vdd rtc in the power detect block. So, the total current is $6.5 \mu A$ on vdd rtc when the ring oscillator is not running.
Bias resistor		14 M Ω		This integrated bias resistor sets the amplifier into a high gain state. Any leakage through the ESD network, external board leakage, or even a scope probe that is significant relative to this value will debias the amp. The debiasing will result in low gain, and will impact the circuit's ability to start up and maintain oscillations.

Table 21. OSC32K Main Characteristics

Table 21. OSC32K Main Characteristics

4.6 I/O DC parameters

This section includes the DC parameters of the following I/O types:

- XTALI and RTC_XTALI (Clock Inputs) DC Parameters
- General Purpose I/O (GPIO)
- Double Data Rate I/O (DDR) for LPDDR2 and DDR3 modes
- LVDS I/O DC Parameters

NOTE

The term 'OVDD' in this section refers to the associated supply rail of an input or output.

Figure 3. Circuit for Parameters Voh and Vol for I/O Cells

4.6.1 XTALI and RTC_XTALI (Clock Inputs) DC parameters

[Table 22](#page-33-1) shows the DC parameters for the clock inputs.

Table 22. XTALI and RTC_XTALI DC Parameters¹

 1 The DC parameters are for external clock input only.

4.6.2 Single voltage General Purpose I/O (GPIO) DC parameters

[Table 23](#page-34-1) shows DC parameters for GPIO pads. The parameters in [Table 23](#page-34-1) are guaranteed per the operating ranges in [Table 10](#page-22-0), unless otherwise noted.

Table 23. Single Voltage GPIO DC Parameters

 1 Overshoot and undershoot conditions (transitions above OVDD and below GND) on switching pads must be held below 0.6 V, and the duration of the overshoot/undershoot must not exceed 10% of the system clock cycle. Overshoot/ undershoot must be controlled through printed circuit board layout, transmission line impedance matching, signal line termination, or other methods. Non-compliance to this specification may affect device reliability or cause permanent damage to the device.

- $2\,$ To maintain a valid level, the transition edge of the input must sustain a constant slew rate (monotonic) from the current DC level through to the target DC level, Vil or Vih. Monotonic input transition time is from 0.1 ns to 1 s.
- 3 Hysteresis of 250 mV is guaranteed over all operating conditions when hysteresis is enabled.

4.6.3 DDR I/O DC parameters

The DDR I/O pads support LPDDR2 and DDR3/DDR3L operational modes. For details on supported DDR memory configurations, see [Section 4.10, "Multi-Mode DDR Controller \(MMDC\)"](#page-52-0).

MMDC operation with the standards stated above is contingent upon the board DDR design adherence to the DDR design and layout requirements stated in the *Hardware Development Guide for the i.MX 6UltraLite Applications Processor* (IMX6ULHDG).

4.6.3.1 LPDDR2 mode I/O DC parameters

Table 24. LPDDR2 I/O DC Electrical Parameters¹

Note that the JEDEC LPDDR2 specification (JESD209_2B) supersedes any specification in this document.

² The single-ended signals need to be within the respective limits (Vih(dc) max, Vil(dc) min) for single-ended signals as well as the limitations for overshoot and undershoot.

4.6.3.2 DDR3/DDR3L mode I/O DC parameters

The parameters in [Table 26](#page-35-3) are guaranteed per the operating ranges in [Table 10,](#page-22-0) unless otherwise noted.

Table 26. DDR3/DDR3L I/O DC Electrical Characteristics

Parameters	Symbol	Test Conditions	Min	Max	Unit
High-level output voltage	VOH	$\text{loh} = -0.1 \text{mA}$ Voh (for ipp dse=001)	$0.8*$ OVDD ¹		
Low-level output voltage	VOL	$IoI = 0.1mA$ Vol (for ipp_dse=001)	0.2^{\ast} OVDD		
Parameters	Symbol	Test Conditions	Min	Max	Unit
--	-------------	--	--------------	--------------	-----------
High-level output voltage	VOH	$loh = -1mA$ Voh (for all except ipp_dse=001)	$0.8*$ OVDD		V
Low-level output voltage	VOL	$IoI = 1mA$ Vol (for all except ipp_dse=001)	$0.2*$ OVDD		\vee
Input Reference Voltage	Vref		0.49 *ovdd	0.51 *ovdd	\vee
DC High-Level input voltage	Vih_DC		$Vref2+0.1$	OVDD	\vee
DC Low-Level input voltage	Vil_DC		OVSS	$Vref-0.1$	\vee
Differential Input Logic High	Vih_diff		0.2		\vee
Differential Input Logic Low	Vil_diff			-0.2	\vee
Termination Voltage	Vtt	Vtt tracking OVDD/2	0.49 *OVDD	$0.51*$ OVDD	\vee
Pull-up/Pull-down Impedance Mismatch	Mmpupd		-10	10	%
240 Ω unit calibration resolution	Rres			10	Ω
Keeper Circuit Resistance	Rkeep		105	165	$k\Omega$
Input current (no pull-up/down)	lin	$VI = 0.VI = OVDD$	-2.9	2.9	μA

Table 26. DDR3/DDR3L I/O DC Electrical Characteristics (continued)

¹ OVDD – I/O power supply (1.425 V–1.575 V for DDR3 and 1.283 V–1.45 V for DDR3L)

² Vref – DDR3/DDR3L external reference voltage

4.6.4 LVDS I/O DC parameters

The LVDS interface complies with TIA/EIA 644-A standard. See TIA/EIA STANDARD 644-A, "Electrical Characteristics of Low Voltage Differential Signaling (LVDS) Interface Circuits" for details.

[Table 27](#page-36-0) shows the Low Voltage Differential Signaling (LVDS) I/O DC parameters.

Table 27. LVDS I/O DC Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Output Differential Voltage	VOD	Rload-100 Ω Diff	250	350	450	mV
Output High Voltage	VOH	$IOH = 0mA$	1.25	1.375	1.6	v
Output Low Voltage	VOL	$1OL = 0 mA$	0.9	1.025	1.25	
Offset Voltage	VOS		1.125	1.2	1.375	

4.7 I/O AC parameters

This section includes the AC parameters of the following I/O types:

- General Purpose I/O (GPIO)
- Double Data Rate I/O (DDR) for LPDDR2 and DDR3/DDR3L modes

The GPIO and DDR I/O load circuit and output transition time waveforms are shown in [Figure 4](#page-37-0) and [Figure 5](#page-37-1).

CL includes package, probe and fixture capacitance

Figure 4. Load Circuit for Output

Figure 5. Output Transition Time Waveform

4.7.1 General Purpose I/O AC parameters

The I/O AC parameters for GPIO in slow and fast modes are presented in the [Table 28](#page-37-2) and [Table 29,](#page-38-0) respectively. Note that the fast or slow I/O behavior is determined by the appropriate control bits in the IOMUXC control registers.

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Output Pad Transition Times, rise/fall (Max Drive, ipp dse=111)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate			2.72/2.79 1.51/1.54	
Output Pad Transition Times, rise/fall (High Drive, ipp dse=101)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate			3.20/3.36 1.96/2.07	ns
Output Pad Transition Times, rise/fall (Medium Drive, ipp dse=100)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate			3.64/3.88 2.27/2.53	
Output Pad Transition Times, rise/fall (Low Drive. ipp dse=011)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate			4.32/4.50 3.16/3.17	
Input Transition Times ¹	trm				25	ns

Table 28. General Purpose I/O AC Parameters 1.8 V Mode

 1 Hysteresis mode is recommended for inputs with transition times greater than 25 ns.

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Output Pad Transition Times, rise/fall (Max Drive, ipp dse=101)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate			1.70/1.79 1.06/1.15	
Output Pad Transition Times, rise/fall (High Drive, ipp dse=011)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate			2.35/2.43 1.74/1.77	ns
Output Pad Transition Times, rise/fall (Medium Drive, ipp dse=010)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate			3.13/3.29 2.46/2.60	
Output Pad Transition Times, rise/fall (Low Drive. ipp dse=001)	tr, tf	15 pF Cload, slow slew rate 15 pF Cload, fast slew rate			5.14/5.57 4.77/5.15	ns
Input Transition Times ¹	trm				25	ns

Table 29. General Purpose I/O AC Parameters 3.3 V Mode

 $\frac{1}{1}$ Hysteresis mode is recommended for inputs with transition times greater than 25 ns.

4.7.2 DDR I/O AC parameters

The Multi-mode DDR Controller (MMDC) is compatible with JEDEC-compliant SDRAMs. For details on supported DDR memory configurations, see [Section 4.10, "Multi-Mode DDR Controller \(MMDC\)".](#page-52-0)

MMDC operation with the standards stated above is contingent upon the board DDR design adherence to the DDR design and layout requirements stated in the *Hardware Development Guide for the i.MX 6UltraLite Applications Processor* (IMX6ULHDG).

[Table 30](#page-38-1) shows the AC parameters for DDR I/O operating in LPDDR2 mode.

Parameter	Symbol	Test Condition	Min	Max	Unit
AC input logic high	Vih(ac)		$Vref + 0.22$	OVDD	v
AC input logic low	Vil(ac)		0	Vref - 0.22	V
AC differential input high voltage ²	Vidh(ac)		0.44		v
AC differential input low voltage	Vidl(ac)			0.44	V
Input AC differential cross point voltage ³	Vix(ac)	Relative to Vref	-0.12	0.12	v
Over/undershoot peak	Vpeak			0.35	v
Over/undershoot area (above OVDD or below OVSS)	Varea	400 MHz		0.3	$V-ns$

Table 30. DDR I/O LPDDR2 Mode AC Parameters1

Table 30. DDR I/O LPDDR2 Mode AC Parameters1 (continued)

¹ Note that the JEDEC LPDDR2 specification (JESD209_2B) supersedes any specification in this document.

² Vid(ac) specifies the input differential voltage | Vtr - Vcp | required for switching, where Vtr is the "true" input signal and Vcp is the "complementary" input signal. The Minimum value is equal to Vih(ac) - Vil(ac).

 3 The typical value of Vix(ac) is expected to be about 0.5 x OVDD. and Vix(ac) is expected to track variation of OVDD. Vix(ac) indicates the voltage at which differential input signal must cross.

[Table 31](#page-39-0) shows the AC parameters for DDR I/O operating in DDR3/DDR3L mode.

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
AC input logic high	Vih(ac)		$Vref + 0.175$		OVDD	V
AC input logic low	Vil(ac)		0		Vref - 0.175	\vee
AC differential input voltage ²	Vid(ac)		0.35			V
Input AC differential cross point voltage ³	Vix(ac)	Relative to Vref	Vref - 0.15		Vref $+0.15$	\vee
Over/undershoot peak	Vpeak				0.4	\vee
Over/undershoot area (above OVDD or below OVSS)	Varea	400 MHz			0.5	V-ns
Single output slew rate, measured between Vol (ac) and Voh (ac)	tsr	Driver impedance = 34 Ω	2.5		5	V/ns
Skew between pad rise/fall asymmetry + skew caused by SSN	t_{SKD}	$clk = 400 MHz$			0.1	ns

Table 31. DDR I/O DDR3/DDR3L Mode AC Parameters¹

 1 Note that the JEDEC JESD79_3D specification supersedes any specification in this document.

² Vid(ac) specifies the input differential voltage | Vtr-Vcp | required for switching, where Vtr is the "true" input signal and Vcp is the "complementary" input signal. The Minimum value is equal to Vih(ac) - Vil(ac).

 3 The typical value of Vix(ac) is expected to be about 0.5 x OVDD. and Vix(ac) is expected to track variation of OVDD. Vix(ac) indicates the voltage at which differential input signal must cross.

4.8 Output buffer impedance parameters

This section defines the I/O impedance parameters of the i.MX 6UltraLite processors for the following I/O types:

• Single Voltage General Purpose I/O (GPIO)

• Double Data Rate I/O (DDR) for LPDDR2, and DDR3/DDR3L modes

NOTE

GPIO and DDR I/O output driver impedance is measured with "long" transmission line of impedance Ztl attached to I/O pad and incident wave launched into transmission line. Rpu/Rpd and Ztl form a voltage divider that defines specific voltage of incident wave relative to OVDD. Output driver impedance is calculated from this voltage divider (see [Figure 6](#page-40-0)).

4.8.1 Single voltage GPIO output buffer impedance

[Table 32](#page-41-0) shows the GPIO output buffer impedance (OVDD 1.8 V).

Table 32. GPIO Output Buffer Average Impedance (OVDD 1.8 V)

Parameter	Symbol	Drive Strength (DSE)	Typ Value	Unit
		001	260	
		010	130	
Output Driver	Rdrv	011	88	
Impedance		100	65	Ω
		101	52	
		110	43	
		111	37	

[Table 33](#page-41-1) shows the GPIO output buffer impedance (OVDD 3.3 V).

Table 33. GPIO Output Buffer Average Impedance (OVDD 3.3 V)

4.8.2 DDR I/O output buffer impedance

[Table 34](#page-41-2) shows DDR I/O output buffer impedance of i.MX 6UltraLite processors.

Table 34. DDR I/O Output Buffer Impedance

Note:

1. Output driver impedance is controlled across PVTs using ZQ calibration procedure.

2. Calibration is done against 240 Ω external reference resistor.

3. Output driver impedance deviation (calibration accuracy) is ±5% (max/min impedance) across PVTs.

4. It is recommended to use a strong driver strength $(<= 48 \Omega)$ for all DDR pads and all DDR type (DDR3/DDR3L/LPDDR2).

4.9 System modules timing

This section contains the timing and electrical parameters for the modules in each i.MX 6UltraLite processor.

4.9.1 Reset timings parameters

[Figure 7](#page-42-0) shows the reset timing and [Table 35](#page-42-1) lists the timing parameters.

Figure 7. Reset Timing Diagram

4.9.2 WDOG reset timing parameters

[Figure 8](#page-42-2) shows the WDOG reset timing and [Table 36](#page-42-3) lists the timing parameters.

Figure 8. WDOGn_B Timing Diagram

Table 36. WDOGn_B Timing Parameters

ID	Parameter	Min	Max	Unit
CC ₃	Duration of WDOGn B Assertion			RTC XTALI cycle

NOTE

RTC_XTALI is approximately 32 kHz. RTC_XTALI cycle is one period or approximately $30 \mu s$.

NOTE

WDOG1 B output signals (for each one of the Watchdog modules) do not have dedicated pins, but are muxed out through the IOMUX. See the IOMUX manual for detailed information.

4.9.3 External Interface Module (EIM)

The following subsections provide information on the EIM. Maximum operating frequency for EIM data transfer is 104 MHz. Timing parameters in this section that are given as a function of register settings or clock periods are valid for the entire range of allowed frequencies (0–104 MHz).

4.9.3.1 EIM interface pads allocation

EIM supports 16-bit and 8-bit devices operating in address/data separate or multiplexed modes. [Table 37](#page-43-0) provides EIM interface pads allocation in different modes.

	Address/Data Non Multiplexed Address/Data Mode									
Setup			8 Bit			16 Bit	16 Bit			
	$MUM = 0$, $DSZ = 100$	$MUM = 0$, $DSZ = 101$	$MUM = 0$, $DSZ = 110$	$MUM = 0$, $DSZ = 111$	$MUM = 0$, $DSZ = 001$	$MUM = 0$ $DSZ = 010$	$MUM = 1$, $DSZ = 001$			
EIM ADDR [15:00]	EIM AD [15:00]	EIM AD $[15:00]$	EIM AD [15:00]	EIM AD [15:00]	EIM AD [15:00]	EIM AD [15:00]	EIM AD [15:00]			
EIM ADDR [26:16]	EIM ADDR [26:16]	EIM ADDR [26:16]	EIM ADDR [26:16]	EIM ADDR [26:16]	EIM ADDR [26:16]	EIM ADDR [26:16]	EIM ADDR [26:16]			
EIM DATA $[07:00]$, EIM EB0 B	EIM DATA [07:00]		Reserved	Reserved	EIM DATA [07:00]	Reserved	EIM AD [07:00]			
EIM DATA $[15:08]$, EIM EB1 B		EIM DATA [15:08]	Reserved	Reserved	EIM DATA [15:08]	Reserved	EIM AD [15:08]			

Table 37. EIM Internal Module Multiplexing¹

¹ For more information on configuration ports mentioned in this table, see the *i.MX 6UltraLite Reference Manual (IMX6ULRM)*.

General EIM Timing-Synchronous Mode

[Figure 9](#page-44-0), [Figure 10,](#page-44-1) and [Table 38](#page-44-2) specify the timings related to the EIM module. All EIM output control signals may be asserted and deasserted by an internal clock synchronized to the EIM_BCLK rising edge according to corresponding assertion/negation control fields.

Figure 9. EIM Outputs Timing Diagram

Figure 10. EIM Inputs Timing Diagram

4.9.3.2 Examples of EIM synchronous accesses

Table 38. EIM Bus Timing Parameters

ID	Parameter	Min ¹	Max ¹	Unit
WE5	Clock rise to address invalid	-0.5 x t x (k + 1) - 1.25	-0.5 x t x (k + 1) + 2.25	ns
WE6	Clock rise to EIM_CSx_B valid	-0.5 x t x (k + 1) - 1.25	-0.5 x t x (k + 1) + 2.25	ns
WE7	Clock rise to EIM CSx B invalid	-0.5 x t x (k + 1) - 1.25	-0.5 x t x (k + 1) + 2.25	ns
WE8	Clock rise to EIM_WE_B Valid	-0.5 x t x (k + 1) - 1.25	-0.5 x t x (k + 1) + 2.25	ns
WE9	Clock rise to EIM_WE_B Invalid	-0.5 x t x (k + 1) - 1.25	-0.5 x t x (k + 1) + 2.25	ns
WE10	Clock rise to EIM OE B Valid	-0.5 x t x (k + 1) - 1.25	-0.5 x t x (k + 1) + 2.25	ns
WE11	Clock rise to EIM OE B Invalid	-0.5 x t x (k + 1) - 1.25	-0.5 x t x (k + 1) + 2.25	ns
WE12	Clock rise to EIM EBx B Valid	-0.5 x t x (k + 1) - 1.25	-0.5 x t x (k + 1) + 2.25	ns
WE13	Clock rise to EIM EBx B Invalid	-0.5 x t x (k + 1) - 1.25	-0.5 x t x (k + 1) + 2.25	ns
WE14	Clock rise to EIM LBA B Valid	-0.5 x t x (k + 1) - 1.25	-0.5 x t x (k + 1) + 2.25	ns
WE15	Clock rise to EIM LBA B Invalid	-0.5 x t x (k + 1) - 1.25	-0.5 x t x (k + 1) + 2.25	ns
WE16	Clock rise to Output Data Valid	-0.5 x t x (k + 1) - 1.25	-0.5 x t x (k + 1) + 2.25	ns
WE17	Clock rise to Output Data Invalid	-0.5 x t x (k + 1) - 1.25	-0.5 x t x (k + 1) + 2.25	ns
WE18	Input Data setup time to Clock rise	2.3		ns
WE19	Input Data hold time from Clock rise	2		ns
WE20	EIM WAIT B setup time to Clock rise	$\overline{2}$		ns
WE21	EIM WAIT B hold time from Clock rise	$\overline{2}$		ns

Table 38. EIM Bus Timing Parameters (continued)

 $\frac{1}{1}$ k represents register setting BCD value.

 2 t is clock period (1/Freq.) For 104 MHz, t = 9.165 ns.

[Figure 11](#page-45-1) to [Figure 14](#page-47-0) provide few examples of basic EIM accesses to external memory devices with the timing parameters mentioned previously for specific control parameters settings.

Figure 11. Synchronous Memory Read Access, WSC=1

NOTE

In 32-bit muxed address/data (A/D) mode the 16 MSBs are driven on the data bus.

Figure 14. 16-Bit Muxed A/D Mode, Synchronous Read Access, WSC=7, RADVN=1, ADH=1, OEA=0

4.9.3.3 General EIM timing-asynchronous mode

[Figure 15](#page-47-1) through [Figure 19,](#page-49-0) and [Table 39](#page-50-0) help to determine timing parameters relative to the chip select (CS) state for asynchronous and DTACK EIM accesses with corresponding EIM bit fields and the timing parameters mentioned above.

Asynchronous read & write access length in cycles may vary from what is shown in [Figure 15](#page-47-1) through [Figure 18](#page-49-1) as RWSC, OEN and CSN is configured differently. See the *i.MX 6UltraLite Reference Manual (IMX6ULRM)* for the EIM programming model.

Figure 15. Asynchronous Memory Read Access (RWSC = 5)

Figure 16. Asynchronous A/D Muxed Read Access (RWSC = 5)

Figure 19. DTACK Mode Read Access (DAP=0)

Figure 20. DTACK Mode Write Access (DAP=0)

Table 39. EIM Asynchronous Timing Parameters Table Relative Chip to Select^{1,2}

Table 39. EIM Asynchronous Timing Parameters Table Relative Chip to Select1,2

¹ For more information on configuration parameters mentioned in this table, see the *i.MX 6UltraLite Reference Manual* (IMX6ULRM).

² In this table, CSA means WCSA when write operation or RCSA when read operation

— t means clock period from axi_clk frequency.

—CSA means register setting for WCSA when in write operations or RCSA when in read operations.

—CSN means register setting for WCSN when in write operations or RCSN when in read operations.

—ADVN means register setting for WADVN when in write operations or RADVN when in read operations.

—ADVA means register setting for WADVA when in write operations or RADVA when in read operations.

4.10 Multi-Mode DDR Controller (MMDC)

The Multi-Mode DDR Controller is a dedicated interface to DDR3/DDR3L/LPDDR2 SDRAM.

4.10.1 MMDC compatibility with JEDEC-compliant SDRAMs

The i.MX 6UltraLite MMDC supports the following memory types:

- LPDDR2 SDRAM compliant with JESD209-2B LPDDR2 JEDEC standard release June, 2009
- DDR3/DDR3L SDRAM compliant with JESD79-3D DDR3 JEDEC standard release April, 2008

MMDC operation with the standards stated above is contingent upon the board DDR design adherence to the DDR design and layout requirements stated in the *Hardware Development Guide for the i.MX 6UltraLite Applications Processor (IMX6ULHDG)*.

4.10.2 MMDC supported DDR3/DDR3L/LPDDR2 configurations

[Table 40](#page-53-0) shows the MMDC supported DDR3/DDR3L/LPDDR2 configurations.

Parameter	DDR ₃	DDR3L	LDDDR2
Clock frequency	400 MHz	400 MHz	400 MHz
l Bus width	16-bit	16-bit	16-bit
Channel	Single	Single	Single
Chip selects		◠	າ ۷

Table 40. i.MX 6UltraLite Supported DDR3/DDR3L/LPDDR2 Configurations

4.11 General-Purpose Media Interface (GPMI) timing

The i.MX 6UltraLite GPMI controller is a flexible interface NAND Flash controller with 8-bit data width, up to 200 MB/s I/O speed and individual chip select.

It supports Asynchronous timing mode, Source Synchronous timing mode and Samsung Toggle timing mode separately described in the following subsections.

4.11.1 Asynchronous mode AC timing (ONFI 1.0 compatible)

Asynchronous mode AC timings are provided as multiplications of the clock cycle and fixed delay. The maximum I/O speed of GPMI in asynchronous mode is about 50 MB/s. [Figure 21](#page-53-1) through [Figure 24](#page-54-0) depicts the relative timing between GPMI signals at the module level for different operations under asynchronous mode. [Table 41](#page-55-0) describes the timing parameters (NF1–NF17) that are shown in the figures.

Figure 21. Command Latch Cycle Timing Diagram

Figure 22. Address Latch Cycle Timing Diagram

Figure 23. Write Data Latch Cycle Timing Diagram

Figure 24. Read Data Latch Cycle Timing Diagram (Non-EDO Mode)

Figure 25. Read Data Latch Cycle Timing Diagram (EDO Mode)

 $¹$ GPMI's Async Mode output timing can be controlled by the module's internal registers</sup> HW_GPMI_TIMING0_ADDRESS_SETUP, HW_GPMI_TIMING0_DATA_SETUP, and HW_GPMI_TIMING0_DATA_HOLD. This AC timing depends on these registers settings. In the table, AS/DS/DH represents each of these settings.

2 AS minimum value can be 0, while DS/DH minimum value is 1.

 3 T = GPMI clock period -0.075ns (half of maximum p-p jitter).

⁴ NF12 is guaranteed by the design.

⁵ Non-EDO mode.

 6 EDO mode, GPMI clock \approx 100 MHz (AS=DS=DH=1, GPMI_CTL1 [RDN_DELAY] = 8, GPMI_CTL1 [HALF_PERIOD] = 0).

In EDO mode [\(Figure 24\)](#page-54-0), NF16/NF17 is different from the definition in non-EDO mode ([Figure 23](#page-54-1)). They are called tREA/tRHOH (RE# access time/RE# HIGH to output hold). The typical values for them are 16 ns (max for tREA)/15 ns (min for tRHOH) at 50 MB/s EDO mode. In EDO mode, GPMI will sample NAND_DATAxx at rising edge of delayed NAND_RE_B provided by an internal DPLL. The delay value can be controlled by GPMI_CTRL1.RDN_DELAY (see the GPMI chapter of the *i.MX 6UltraLite Reference Manual*). The typical value of this control register is 0x8 at 50 MT/s EDO mode. But if the board delay is big enough and cannot be ignored, the delay value should be made larger to compensate the board delay.

4.11.2 Source synchronous mode AC timing (ONFI 2.x compatible)

[Figure 26](#page-56-0) to [Figure 28](#page-57-0) show the write and read timing of Source Synchronous Mode.

Figure 26. Source Synchronous Mode Command and Address Timing Diagram

Figure 29. NAND_DQS/NAND_DQ Read Valid Window

ID	Parameter		Timing T = GPMI Clock Cycle		Unit
			Min.	Max.	
NF18	NAND CE0 B access time	tCE	CE DELAY \times T - 0.79 [see ²]		ns
	NF19 NAND_CE0_B hold time	tCH	$0.5 \times$ tCK - 0.63 [see 2]		ns
NF20	Command/address NAND DATAxx setup time	tCAS	$0.5 \times$ tCK - 0.05		ns
NF21	Command/address NAND_DATAxx hold time	tCAH	$0.5 \times$ tCK - 1.23		ns
NF22	Clock period	tCK			ns
NF23	Preamble delay	tPRE	PRE DELAY \times T - 0.29 [see 2]		ns
	NF24 Postamble delay	tPOST	POST DELAY \times T - 0.78 [see ²]		ns
	NF25 NAND CLE and NAND ALE setup time	tCALS	$0.5 \times$ tCK - 0.86		ns
	NF26 NAND CLE and NAND ALE hold time	tCALH	$0.5 \times$ tCK - 0.37		ns
NF27	NAND_CLK to first NAND_DQS latching transition	tDQSS	T - 0.41 [see 2]		ns
NF28	Data write setup		$0.25 \times tCK - 0.35$		
NF29	Data write hold		$0.25 \times$ tCK - 0.85		
	NF30 NAND_DQS/NAND_DQ read setup skew		2.06		
	NF31 NAND_DQS/NAND_DQ read hold skew			1.95	

Table 42. Source Synchronous Mode Timing Parameters1

 1 GPMI's source synchronous mode output timing can be controlled by the module's internal registers GPMI_TIMING2_CE_DELAY, GPMI_TIMING_PREAMBLE_DELAY, GPMI_TIMING2_POST_DELAY. This AC timing depends on these registers settings. In the table, CE_DELAY/PRE_DELAY/POST_DELAY represents each of these settings.

² T = tCK(GPMI clock period) -0.075ns (half of maximum p-p jitter).

For DDR Source sync mode, [Figure 29](#page-58-1) shows the timing diagram of NAND_DQS/NAND_DATAxx read valid window. The typical value of tDQSQ is 0.85ns (max) and 1ns (max) for tQHS at 200MB/s. GPMI will sample NAND_DATA[7:0] at both rising and falling edge of a delayed NAND_DQS signal, which can be provided by an internal DPLL. The delay value can be controlled by GPMI register GPMI_READ_DDR_DLL_CTRL.SLV_DLY_TARGET (see the GPMI chapter of the *i.MX 6UltraLite Reference Manual*). Generally, the typical delay value of this register is equal to 0x7 which means 1/4 clock cycle delay expected. But if the board delay is big enough and cannot be ignored, the delay value should be made larger to compensate the board delay.

4.11.3 Samsung toggle mode AC timing

4.11.3.1 Command and address timing

NOTE

Samsung Toggle Mode command and address timing is the same as ONFI 1.0 compatible Async mode AC timing. See [Section 4.11.1, "Asynchronous](#page-53-2) [mode AC timing \(ONFI 1.0 compatible\)",](#page-53-2)" for details.

4.11.3.2 Read and write timing

Figure 30. Samsung Toggle Mode Data Write Timing

Figure 31. Samsung Toggle Mode Data Read Timing

Table 43. Samsung Toggle Mode Timing Parameters1 (continued)

 1 The GPMI toggle mode output timing can be controlled by the module's internal registers HW_GPMI_TIMING0_ADDRESS_SETUP, HW_GPMI_TIMING0_DATA_SETUP, and HW_GPMI_TIMING0_DATA_HOLD. This AC timing depends on these registers settings. In the table, AS/DS/DH represents each of these settings.

2 AS minimum value can be 0, while DS/DH minimum value is 1.

 3 T = tCK (GPMI clock period) -0.075ns (half of maximum p-p jitter).

⁴ CE_DELAY represents HW_GPMI_TIMING2[CE_DELAY]. NF18 is guaranteed by the design. Read/Write operation is started with enough time of ALE/CLE assertion to low level.

 5 PRE DELAY+1) \geq (AS+DS)

⁶ Shown in [Figure 30.](#page-59-0)

⁷ Shown in [Figure 31.](#page-60-0)

For DDR Toggle mode, [Figure 29](#page-58-1) shows the timing diagram of NAND_DQS/NAND_DATAxx read valid window. The typical value of tDQSQ is 1.4 ns (max) and 1.4 ns (max) for tQHS at 133 MB/s. GPMI will sample NAND DATA[7:0] at both rising and falling edge of an delayed NAND DQS signal, which is provided by an internal DPLL. The delay value of this register can be controlled by GPMI register GPMI_READ_DDR_DLL_CTRL.SLV_DLY_TARGET (see the GPMI chapter of the *i.MX 6UltraLite Reference Manual*). Generally, the typical delay value is equal to 0x7 which means 1/4 clock cycle delay expected. But if the board delay is big enough and cannot be ignored, the delay value should be made larger to compensate the board delay.

4.12 External peripheral interface parameters

The following subsections provide information on external peripheral interfaces.

4.12.1 CMOS Sensor Interface (CSI) timing parameters

4.12.1.0.1 Gated clock mode timing

[Figure 32](#page-62-0) and [Figure 33](#page-62-1) shows the gated clock mode timings for CSI, and [Table 44](#page-62-2) describes the timing parameters (P1–P7) shown in the figures. A frame starts with a rising/falling edge on CSI_VSYNC

(VSYNC), then CSI_HSYNC (HSYNC) is asserted and holds for the entire line. The pixel clock, CSI_PIXCLK (PIXCLK), is valid as long as HSYNC is asserted.

Figure 32. CSI Gated Clock Mode—Sensor Data at Falling Edge, Latch Data at Rising Edge

Figure 33. CSI Gated Clock Mode—Sensor Data at Rising Edge, Latch Data at Falling Edge

4.12.1.0.2 Ungated clock mode timing

[Figure 34](#page-63-0) shows the ungated clock mode timings of CSI, and [Table 45](#page-63-1) describes the timing parameters (P1–P6) that are shown in the figure. In ungated mode the CSI_VSYNC and CSI_PIXCLK signals are used, and the CSI_HSYNC signal is ignored.

Figure 34. CSI Ungated Clock Mode—Sensor Data at Falling Edge, Latch Data at Rising Edge

ID	Parameter	Symbol	Min.	Max.	Units
P ₁	CSI VSYNC to pixel clock time	tVSYNC	33.5		ns
P ₂	CSI DATA setup time	tDsu			ns
P ₃	CSI DATA hold time	tDh			ns
P4	CSI pixel clock high time	tCLKh	3.75		ns
P ₅	CSI pixel clock low time	tCLKI	3.75		ns
P ₆	CSI pixel clock frequency	fCLK		133	MHz

Table 45. CSI Ungated Clock Mode Timing Parameters

The CSI enables the chip to connect directly to external CMOS image sensors, which are classified as dumb or smart as follows:

- Dumb sensors only support traditional sensor timing (vertical sync (VSYNC) and horizontal sync (HSYNC)) and output-only Bayer and statistics data.
- Smart sensors support CCIR656 video decoder formats and perform additional processing of the image (for example, image compression, image pre-filtering, and various data output formats).

The following subsections describe the CSI timing in gated and ungated clock modes.

4.12.2 ECSPI timing parameters

This section describes the timing parameters of the ECSPI blocks. The ECSPI have separate timing parameters for master and slave modes.

4.12.2.1 ECSPI master mode timing

[Figure 35](#page-64-0) depicts the timing of ECSPI in master mode. [Table 46](#page-64-1) lists the ECSPI master mode timing characteristics.

Figure 35. ECSPI Master Mode Timing Diagram

¹ See specific I/O AC parameters [Section 4.7, "I/O AC parameters".](#page-36-1)"

 2 SPI_RDY is sampled internally by ipg_clk and is asynchronous to all other CSPI signals.

4.12.2.2 ECSPI slave mode timing

[Figure 36](#page-65-0) depicts the timing of ECSPI in slave mode. [Table 47](#page-65-1) lists the ECSPI slave mode timing characteristics.

Figure 36. ECSPI Slave Mode Timing Diagram

Table 47. ECSPI Slave Mode Timing Parameters

4.12.3 Ultra High Speed SD/SDIO/MMC Host Interface (uSDHC) AC timing

This section describes the electrical information of the uSDHC, which includes SD/eMMC4.3 (Single Data Rate) timing, eMMC4.4/4.41/4.5 (Dual Date Rate) timing and SDR104/50(SD3.0) timing.

4.12.3.1 SD/eMMC4.3 (single data rate) AC timing

[Figure 37](#page-66-0) depicts the timing of SD/eMMC4.3, and [Table 48](#page-66-1) lists the SD/eMMC4.3 timing characteristics.

Figure 37. SD/eMMC4.3 Timing

Table 48. SD/eMMC4.3 Interface Timing Specification (continued)

¹ In low speed mode, card clock must be lower than 400 kHz, voltage ranges from 2.7 to 3.6 V.
² In normal (full) speed mode for SD/SDIO card, clock frequency can be any value between 0-

In normal (full) speed mode for SD/SDIO card, clock frequency can be any value between 0–25 MHz. In high-speed mode, clock frequency can be any value between 0–50 MHz.

⁴ To satisfy hold timing, the delay difference between clock input and cmd/data input must not exceed 2 ns.

4.12.3.2 eMMC4.4/4.41 (dual data rate) AC timing

[Figure 38](#page-67-0) depicts the timing of eMMC4.4/4.41. [Table 49](#page-67-1) lists the eMMC4.4/4.41 timing characteristics. Be aware that only DATA is sampled on both edges of the clock (not applicable to CMD).

Figure 38. eMMC4.4/4.41 Timing

Table 49. eMMC4.4/4.41 Interface Timing Specification

 3 In normal (full) speed mode for MMC card, clock frequency can be any value between $0-20$ MHz. In high-speed mode, clock frequency can be any value between 0–52 MHz.

4.12.3.3 SDR50/SDR104 AC timing

[Figure 39](#page-68-0) depicts the timing of SDR50/SDR104, and [Table 50](#page-68-1) lists the SDR50/SDR104 timing characteristics.

Figure 39. SDR50/SDR104 Timing

Table 50. SDR50/SDR104 Interface Timing Specification

¹Data window in SDR104 mode is variable.

4.12.3.4 HS200 mode timing

[Figure 40](#page-69-0) depicts the timing of HS200 mode, and [Table 51](#page-69-1) lists the HS200 timing characteristics.

Figure 40. HS200 Mode Timing

ID	Parameter	Symbols	Min	Max	Unit				
Card Input Clock									
SD ₁	Clock Frequency Period	t_{CLK}	5.0		ns				
SD ₂	Clock Low Time	t_{CL}	0.46 x t_{CLK}	$0.54 \times t_{CLK}$	ns				
SD ₃	Clock High Time	t_{CH}	0.46 x t_{CLK}	$0.54 \times t_{CLK}$	ns				
uSDHC Output/Card Inputs SD_CMD, SDx_DATAx in HS200 (Reference to CLK)									
SD ₅	uSDHC Output Delay	t_{OD}	-1.6	0.74	ns				
uSDHC Input/Card Outputs SD_CMD, SDx_DATAx in HS200 (Reference to CLK) ¹									
SD ₈	Card Output Data Window	t_{ODW}	$0.5 \times t_{CLK}$		ns				

Table 51. HS200 Interface Timing Specification

 1 HS200 is for 8 bits while SDR104 is for 4 bits.

4.12.3.5 Bus operation condition for 3.3 V and 1.8 V signaling

Signaling level of SD/eMMC4.3 and eMMC4.4/4.41 modes is 3.3 V. Signaling level of SDR104/SDR50 mode is 1.8 V. The DC parameters for the NVCC SD1 supply are identical to those shown in Table 23, ["Single Voltage GPIO DC Parameters," on page 35.](#page-34-0)

4.12.4 Ethernet Controller (ENET) AC electrical specifications

The following timing specs are defined at the chip I/O pin and must be translated appropriately to arrive at timing specs/constraints for the physical interface.

4.12.4.1 ENET MII mode timing

This subsection describes MII receive, transmit, asynchronous inputs, and serial management signal timings.

4.12.4.1.1 MII receive signal Timing (ENET_RX_DATA3,2,1,0, ENET_RX_EN, ENET_RX_ER, and ENET_RX_CLK)

The receiver functions correctly up to an ENET_RX_CLK maximum frequency of 25 MHz + 1%. There is no minimum frequency requirement. Additionally, the processor clock frequency must exceed twice the ENET RX CLK frequency.

[Figure 41](#page-70-0) shows MII receive signal timings. [Table 52](#page-70-1) describes the timing parameters (M1–M4) shown in the figure.

Figure 41. MII Receive Signal Timing Diagram

¹ ENET_RX_EN, ENET_RX_CLK, and ENET0_RXD0 have the same timing in 10 Mbps 7-wire interface mode.

4.12.4.1.2 MII transmit signal timing (ENET_TX_DATA3,2,1,0, ENET_TX_EN, ENET_TX_ER, and ENET_TX_CLK)

The transmitter functions correctly up to an ENET_TX_CLK maximum frequency of 25 MHz + 1%. There is no minimum frequency requirement. Additionally, the processor clock frequency must exceed twice the ENET TX CLK frequency.

[Figure 42](#page-71-0) shows MII transmit signal timings. [Table 53](#page-71-1) describes the timing parameters (M5–M8) shown in the figure.

Figure 42. MII Transmit Signal Timing Diagram

Table 53. MII Transmit Signal Timing

ID	Characteristic ¹	Min.	Max.	Unit
M ₅	ENET TX CLK to ENET TX DATA3,2,1,0, ENET TX EN, ENET TX ER invalid	5		ns
M ₆	ENET TX CLK to ENET TX DATA3,2,1,0, ENET TX EN, ENET TX ER valid		20	ns
M ₇	ENET TX CLK pulse width high	35%	65%	ENET TX CLK period
M ₈	ENET TX CLK pulse width low	35%	65%	ENET TX CLK period

¹ ENET_TX_EN, ENET_TX_CLK, and ENET0_TXD0 have the same timing in 10-Mbps 7-wire interface mode.

4.12.4.1.3 MII asynchronous inputs signal timing (ENET_CRS and ENET_COL)

[Figure 43](#page-71-2) shows MII asynchronous input timings. [Table 54](#page-71-3) describes the timing parameter (M9) shown in the figure.

Figure 43. MII Async Inputs Timing Diagram

 1 ENET_COL has the same timing in 10-Mbit 7-wire interface mode.
4.12.4.1.4 MII serial management channel timing (ENET_MDIO and ENET_MDC)

The MDC frequency is designed to be equal to or less than 2.5 MHz to be compatible with the IEEE 802.3 MII specification. However the ENET can function correctly with a maximum MDC frequency of 15 MHz.

[Figure 44](#page-72-0) shows MII asynchronous input timings. [Table 55](#page-72-1) describes the timing parameters (M10–M15) shown in the figure.

Figure 44. MII Serial Management Channel Timing Diagram

4.12.4.2 RMII mode timing

In RMII mode, ENET CLK is used as the REF CLK, which is a 50 MHz \pm 50 ppm continuous reference clock. ENET RX EN is used as the ENET RX EN in RMII. Other signals under RMII mode include ENET TX EN, ENET_TX_DATA[1:0], ENET_RX_DATA[1:0] and ENET_RX_ER.

[Figure 45](#page-73-0) shows RMII mode timings. [Table 56](#page-73-1) describes the timing parameters (M16–M21) shown in the figure.

Figure 45. RMII Mode Signal Timing Diagram

4.12.5 Flexible Controller Area Network (FLEXCAN) AC electrical specifications

The Flexible Controller Area Network (FlexCAN) module is a communication controller implementing the CAN protocol according to the CAN 2.0B protocol specification. The processor has two CAN modules available for systems design. Tx and Rx ports for both modules are multiplexed with other I/O pins. See the IOMUXC chapter of the *i.MX 6UltraLite Reference Manual* (IMX6ULRM) to see which pins expose Tx and Rx pins; these ports are named FLEXCAN_TX and FLEXCAN_RX, respectively.

4.12.6 I2C module timing parameters

This section describes the timing parameters of the I^2C module. [Figure 46](#page-74-3) depicts the timing of I^2C module, and [Table 57](#page-74-4) lists the $I^2\overline{C}$ module timing characteristics.

Figure 46. I2C Bus Timing

 1 A device must internally provide a hold time of at least 300 ns for I2Cx_SDA signal to bridge the undefined region of the falling edge of I2Cx_SCL.

² The maximum hold time has only to be met if the device does not stretch the LOW period (ID no IC5) of the I2Cx_SCL signal.

 $3\,$ A Fast-mode I²C-bus device can be used in a Standard-mode I²C-bus system, but the requirement of Set-up time (ID No IC7) of 250 ns must be met. This automatically is the case if the device does not stretch the LOW period of the I2Cx_SCL signal. If such a device does stretch the LOW period of the I2Cx SCL signal, it must output the next data bit to the I2Cx SDA line max rise time (IC9) + data setup time (IC7) = 1000 + 250 = 1250 ns (according to the Standard-mode I²C-bus specification) before the I2Cx_SCL line is released.

 4 C_h = total capacitance of one bus line in pF.

4.12.7 Pulse Width Modulator (PWM) timing parameters

This section describes the electrical information of the PWM. The PWM can be programmed to select one of three clock signals as its source frequency. The selected clock signal is passed through a prescaler before being input to the counter. The output is available at the pulse-width modulator output (PWMO) external pin.

[Figure 47](#page-75-1) depicts the timing of the PWM, and [Table 58](#page-75-2) lists the PWM timing parameters.

Figure 47. PWM Timing

4.12.8 LCD Controller (LCDIF) parameters

[Figure 48](#page-75-0) shows the LCDIF timing and [Table 59](#page-76-0) lists the timing parameters.

Figure 48. LCD Timing

Table 59. LCD Timing Parameters

4.12.8.1 LCDIF signal mapping

[Table 60](#page-76-1) lists the details about the mapping signals.

Table 60. LCD Signal Parameters

Table 60. LCD Signal Parameters (continued)

4.12.9 QUAD SPI (QSPI) timing parameters

Measurement conditions are with 35 pF load on SCK and SIO pins and input slew rate of 1 V/ns.

4.12.9.1 SDR mode

Figure 49. QuadSPI Input/Read Timing (SDR mode with internal sampling)

Table 61. QuadSPI Input Timing (SDR mode with internal sampling)

Figure 50. QuadSPI Input/Read Timing (SDR mode with loopback DQS sampling)

NOTE

- For internal sampling, the timing values assumes using sample point 0, that is QuadSPIx $SMPR[SDRSMP] = 0$.
- For loopback DQS sampling, the data strobe is output to the DQS pad together with the serial clock. The data strobe is looped back from DQS pad and used to sample input data.

Figure 51. QuadSPI Output/Write Timing (SDR mode)

Table 63. QuadSPI Output/Write Timing (SDR mode)

NOTE

 T_{css} and T_{csh} are configured by the QuadSPIx_FLSHCR register, the default value of 3 are shown on the timing. Please refer to the *i.MX 6UltraLite Reference Manual (IMX6ULRM)* for more details.

4.12.9.2 DDR mode

Figure 52. QuadSPI Input/Read Timing (DDR mode with internal sampling)

Table 64. QuadSPI Input/Read Timing (DDR mode with internal sampling)

Figure 53. QuadSPI Input/Read Timing (DDR mode with loopback DQS sampling)

Table 65. QuadSPI Input/Read Timing (DDR mode with loopback DQS sampling)

NOTE

- For internal sampling, the timing values assumes using sample point 0, that is QuadSPIx $SMPR[SDRSMP] = 0$.
- For loopback DQS sampling, the data strobe is output to the DQS pad together with the serial clock. The data strobe is looped back from DQS pad and used to sample input data.

Figure 54. QuadSPI Output/Write Timing (DDR mode)

Table 66. QuadSPI Output/Write Timing (DDR mode)

Table 66. QuadSPI Output/Write Timing (DDR mode)

NOTE

 T_{css} and T_{csh} are configured by the QuadSPIx_FLSHCR register, the default value of 3 are shown on the timing. Please refer to the *i.MX 6UltraLite Reference Manual (IMX6ULRM)* for more details.

4.12.10 SAI/I2S switching specifications

This section provides the AC timings for the SAI in master (clocks driven) and slave (clocks input) modes. All timings are given for non-inverted serial clock polarity (SAI_TCR[TSCKP] = 0, SAI_RCR[RSCKP] = 0) and non-inverted frame sync (SAI_TCR[TFSI] = 0, SAI_RCR[RFSI] = 0). If the polarity of the clock and/or the frame sync have been inverted, all the timings remain valid by inverting the clock signal (SAI_BCLK) and/or the frame sync (SAI_FS) shown in the figures below.

Figure 55. SAI Timing — Master Modes

Figure 56. SAI Timing — Slave Modes

Data **Outputs**

Data **Outputs**

Data Outputs

4.12.11 SCAN JTAG Controller (SJC) timing parameters

SJ6

SJ7

SJ6

[Figure 57](#page-83-0) depicts the SJC test clock input timing. [Figure 58](#page-83-1) depicts the SJC boundary scan timing. [Figure 59](#page-84-0) depicts the SJC test access port. Signal parameters are listed in [Table 69.](#page-84-1)

Figure 58. Boundary Scan (JTAG) Timing Diagram

Output Data Valid

Output Data Valid

ID	Parameter ^{1,2}	All Frequencies	Unit	
		Min	Max	
SJ9	JTAG TMS, JTAG TDI data hold time	25		ns
SJ10	JTAG TCK low to JTAG TDO data valid		44	ns
SJ11	JTAG TCK low to JTAG TDO high impedance		44	ns
SJ12	JTAG TRST_B assert time	100		ns
SJ13	JTAG TRST B set-up time to JTAG TCK low	40		ns

Table 69. JTAG Timing (continued)

 1 T_{DC} = target frequency of SJC

² V_M = mid-point voltage

4.12.12 SPDIF timing parameters

The Sony/Philips Digital Interconnect Format (SPDIF) data is sent using the bi-phase marking code. When encoding, the SPDIF data signal is modulated by a clock that is twice the bit rate of the data signal.

[Table 70](#page-85-0) and [Figure 61](#page-86-0) and [Figure 62](#page-86-1) show SPDIF timing parameters for the Sony/Philips Digital Interconnect Format (SPDIF), including the timing of the modulating Rx clock (SPDIF_SR_CLK) for SPDIF in Rx mode and the timing of the modulating Tx clock (SPDIF ST_CLK) for SPDIF in Tx mode.

Characteristics		Timing Parameter Range	Unit	
	Symbol	Min	Max	
SPDIF_IN Skew: asynchronous inputs, no specs apply			0.7	ns
SPDIF OUT output (Load = 50pf) • Skew • Transition rising • Transition falling			1.5 24.2 31.3	ns
SPDIF_OUT1 output (Load = 30pf) • Skew • Transition rising • Transition falling			1.5 13.6 18.0	ns
Modulating Rx clock (SPDIF_SR_CLK) period	srckp	40.0		ns
SPDIF_SR_CLK high period	srckph	16.0		ns
SPDIF_SR_CLK low period	srckpl	16.0		ns
Modulating Tx clock (SPDIF_ST_CLK) period	stclkp	40.0		ns
SPDIF_ST_CLK high period	stclkph	16.0		ns
SPDIF ST CLK low period	stclkpl	16.0		ns

Table 70. SPDIF Timing Parameters

Figure 62. SPDIF_ST_CLK Timing Diagram

4.12.13 UART I/O configuration and timing parameters

4.12.13.1 UART RS-232 serial mode timing

The following sections describe the electrical information of the UART module in the RS-232 mode.

4.12.13.1.1 UART transmitter

[Figure 63](#page-86-2) depicts the transmit timing of UART in the RS-232 serial mode, with 8 data bit/1 stop bit format. [Table 71](#page-86-3) lists the UART RS-232 serial mode transmits timing characteristics.

Figure 63. UART RS-232 Serial Mode Transmit Timing Diagram

¹ F_{baud_rate}: Baud rate frequency. The maximum baud rate the UART can support is (*ipg_perclk* frequency)/16.

² Tref_clk: The period of UART reference clock *ref_clk* (*ipg_perclk* after RFDIV divider).

4.12.13.1.2 UART receiver

[Figure 64](#page-87-0) depicts the RS-232 serial mode receives timing with 8 data bit/1 stop bit format. [Table 72](#page-87-1) lists serial mode receive timing characteristics.

Figure 64. UART RS-232 Serial Mode Receive Timing Diagram

Table 72. RS-232 Serial Mode Receive Timing Parameters

¹ The UART receiver can tolerate 1/(16 x F_{baud rate}) tolerance in each bit. But accumulation tolerance in one frame must not exceed $3/(16 \times F_{\text{baud rate}})$.

² F_{baud rate}: Baud rate frequency. The maximum baud rate the UART can support is (*ipg_perclk* frequency)/16.

4.12.13.1.3 UART IrDA mode timing

The following subsections give the UART transmit and receive timings in IrDA mode.

UART IrDA mode transmitter

[Figure 65](#page-87-2) depicts the UART IrDA mode transmit timing, with 8 data bit/1 stop bit format. [Table 73](#page-87-3) lists the transmit timing characteristics.

Figure 65. UART IrDA Mode Transmit Timing Diagram

ID	Parameter	Symbol	Min	Max	Unit
UA ₃	Transmit Bit Time in IrDA mode	^l TIRbit	1/F _{baud} _rate ^I ref clk [*]	$1/F_{\text{baud_rate}} + T_{\text{ref_clk}}$	
UA4	Transmit IR Pulse Duration	^I TIRpulse	(3/16) x (1/F _{baud_rate}) + - T _{ref clk}	. _I (3/16) x (1/F _{baud_rate}) + ref_clk	

Table 73. IrDA Mode Transmit Timing Parameters

¹ F_{baud rate}: Baud rate frequency. The maximum baud rate the UART can support is (*ipg_perclk* frequency)/16.

² T_{ref_clk}: The period of UART reference clock *ref_clk* (*ipg_perclk* after RFDIV divider).

UART IrDA mode receiver

[Figure 66](#page-88-0) depicts the UART IrDA mode receive timing, with 8 data bit/1 stop bit format. [Table 74](#page-88-1) lists the receive timing characteristics.

Figure 66. UART IrDA Mode Receive Timing Diagram

Table 74. IrDA Mode Receive Timing Parameters

ID	Parameter	Symbol	Min	Max	Unit
UA ₅	Receive Bit Time ¹ in IrDA mode	^L RIRbit	$\frac{2}{2}$ - 1/(16 1/F _{baud} _rate ² \times F _{baud} _{rate}	$1/F_{\text{baud_rate}} + 1/(16 x)$ Fbaud rate)	
UA6	Receive IR Pulse Duration	^L RIRpulse	$1.41 \text{ }\mu s$	」(5/16) x (1/F _{baud_rate}) ।	

¹ The UART receiver can tolerate 1/(16 x F_{baud rate}) tolerance in each bit. But accumulation tolerance in one frame must not exceed $3/(16 \times F_{\text{baud rate}})$.

² F_{baud rate}: Baud rate frequency. The maximum baud rate the UART can support is (*ipg_perclk* frequency)/16.

4.12.14 USB PHY parameters

This section describes the USB-OTG PHY parameters.

The USB PHY meets the electrical compliance requirements defined in the Universal Serial Bus Revision 2.0 OTG with the following amendments.

- USB ENGINEERING CHANGE NOTICE
	- Title: 5V Short Circuit Withstand Requirement Change
	- Applies to: Universal Serial Bus Specification, Revision 2.0
- Errata for USB Revision 2.0 April 27, 2000 as of 12/7/2000
- USB ENGINEERING CHANGE NOTICE
	- Title: Pull-up/Pull-down resistors
	- Applies to: Universal Serial Bus Specification, Revision 2.0
- USB ENGINEERING CHANGE NOTICE
	- Title: Suspend Current Limit Changes
	- Applies to: Universal Serial Bus Specification, Revision 2.0
- USB ENGINEERING CHANGE NOTICE
	- Title: USB 2.0 Phase Locked SOFs

- Applies to: Universal Serial Bus Specification, Revision 2.0
- On-The-Go and Embedded Host Supplement to the USB Revision 2.0 Specification
	- Revision 2.0 plus errata and ecn June 4, 2010
- Battery Charging Specification (available from USB-IF)
	- Revision 1.2, December 7, 2010
	- Portable device only

4.13 A/D converter

4.13.1 12-bit ADC electrical characteristics

4.13.1.1 12-bit ADC operating conditions

Table 75. 12-bit ADC Operating Conditions

 $\frac{1}{1}$ Typical values assume VDDAD = 3.0 V, Temp = 25°C, f_{ADC} =20 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

² DC potential differences

Figure 67. 12-bit ADC Input Impedance Equivalency Diagram

4.13.1.1.1 12-bit ADC characteristics

Table 76. 12-bit ADC Characteristics (V_{REFH} = V_{DDAD}, V_{REFL} = V_{SSAD})

Characteristic	Conditions ¹	Symb	Min	Type ²	Max	Unit	Comment
[L:] Supply Current	ADLPC=1, ADHSC=0	I DDAD		250		μA	ADLSMP=0 ADSTS=10 ADCO=1
	ADLPC=0. ADHSC=0			350			
	ADLPC=0. ADHSC=1			400			
[L:] Supply Current	Stop, Reset, Module Off	I DDAD		0.01	0.8	μA	
ADC Asynchronous	ADHSC=0	^T ADACK		10		MHz	t_{ADACK} = 1/ f_{ADACK}
Clock Source	ADHSC=1			20			

Characteristic	Conditions ¹	Symb	Min	Type ²	Max	Unit	Comment
Sample Cycles	ADLSMP=0, ADSTS=00	Csamp		$\boldsymbol{2}$		cycles	
	ADLSMP=0, ADSTS=01			$\overline{\mathbf{4}}$			
	ADLSMP=0, ADSTS=10			$\,6\,$			
	ADLSMP=0, ADSTS=11			8			
	ADLSMP=1, ADSTS=00			12			
	ADLSMP=1, ADSTS=01			16			
	ADLSMP=1, ADSTS=10			20			
	ADLSMP=1, ADSTS=11			24			
Conversion Cycles	ADLSMP=0 ADSTS=00	Cconv		28		cycles	
	ADLSMP=0 ADSTS=01			30			
	ADLSMP=0 ADSTS=10			32			
	ADLSMP=0 ADSTS=11			34			
	ADLSMP=1 ADSTS=00			38			
	ADLSMP=1 ADSTS=01			42			
	ADLSMP=1 ADSTS=10			46			
	ADLSMP=1, ADSTS=11			50			

Table 76. 12-bit ADC Characteristics (V_{REFH} = V_{DDAD}, V_{REFL} = V_{SSAD}) (continued)

Table 76. 12-bit ADC Characteristics (V_{REFH} = V_{DDAD}, V_{REFL} = V_{SSAD}) (continued)

 $\overline{1}$ All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDAD}$

 2 Typical values assume V_{DDAD} = 3.0 V, Temp = 25°C, F_{adck}=20 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

NOTE

The ADC electrical spec would be met with the calibration enabled configuration.

This section provides information on boot mode configuration pins allocation and boot devices interfaces allocation.

5.1 Boot mode configuration pins

[Table 77](#page-94-0) provides boot options, functionality, fuse values, and associated pins. Several input pins are also sampled at reset and can be used to override fuse values, depending on the value of BT_FUSE_SEL fuse. The boot option pins are in effect when BT_FUSE_SEL fuse is '0' (cleared, which is the case for an unblown fuse). For detailed boot mode options configured by the boot mode pins, see the i.MX 6UltraLite Fuse Map document and the System Boot chapter in *i.MX 6UltraLite Reference Manual (IMX6ULRM)*.

Pin	Direction at reset	eFuse name	Details
BOOT MODE0	Input with 100 K pull-down	N/A	Boot mode selection
BOOT MODE1	Input with 100 K pull-down	N/A	Boot mode selection

Table 77. Fuses and Associated Pins Used for Boot

5.2 Boot device interface allocation

The following tables list the interfaces that can be used by the boot process in accordance with the specific boot mode configuration. The tables also describe the interface's specific modes and IOMUXC allocation, which are configured during boot when appropriate.

Table 78. QSPI Boot trough QSPI

Table 78. QSPI Boot trough QSPI (continued)

Table 79. SPI Boot through ECSPI1

Table 80. SPI Boot through ECSPI2

Table 80. SPI Boot through ECSPI2 (continued)

Table 81. SPI Boot through ECSPI3

Table 82. SPI Boot through ECSPI4

Table 83. NAND Boot through GPMI

Ball Name	Signal Name	Mux Mode	Common	BOOT_CFG1[3:2]= 01 _b	BOOT_CFG1[3:2]= 10 _b
NAND_DATA00	rawnand.DATA00	Alt ₀	Yes		
NAND DATA01	rawnand.DATA01	Alt 0	Yes		
NAND DATA02	rawnand.DATA02	Alt ₀	Yes		
NAND_DATA03	rawnand.DATA03	Alt 0	Yes		
NAND DATA04	rawnand.DATA04	Alt 0	Yes		
NAND_DATA05	rawnand.DATA05	Alt 0	Yes		
NAND_DATA06	rawnand.DATA06	Alt 0	Yes		
NAND_DATA07	rawnand.DATA07	Alt 0	Yes		
NAND DQS	rawnand.DQS	Alt 0	Yes		
CSI MCLK	rawnand.CE2 B	Alt 2			Yes
CSI PIXCLK	rawnand.CE3 B	Alt 2			Yes

Table 83. NAND Boot through GPMI (continued)

Table 84. SD/MMC Boot through USDHC1

Table 85. SD/MMC Boot through USDHC2

Table 86. NOR/OneNAND Boot through EIM

Table 87. Serial Download through UART1

Table 88. Serial Download through UART2

This section includes the contact assignment information and mechanical package drawing.

6.1 14x14 mm package information

6.1.1 14x14 mm, 0.8 mm pitch, ball matrix

[Figure 68](#page-103-0) shows the top, bottom, and side views of the 14x14 mm BGA package.

6.1.2 14x14 mm supplies contact assignments and functional contact assignments

[Table 89](#page-104-0) shows the device connection list for ground, sense, and reference contact signals.

Table 89. 14x14 mm Supplies Contact Assignment

[Table 90](#page-105-0) shows an alpha-sorted list of functional contact assignments for the 14x14 mm package.

			Ball Type	Out of Reset Condition				
Ball Name	14x14 Ball	Power Group		Default Mode	Default Function	Input/ Output	Value	
BOOT_MODE0	T10	VDD_SNVS_IN	GPIO	ALT5	BOOT MODE0	Input	100 $k\Omega$ pull-down	
BOOT_MODE1	U10	VDD_SNVS_IN	GPIO	ALT5	BOOT_MODE1	Input	100 k Ω pull-down	
CCM CLK1 N	P ₁₆	VDD_HIGH_CAP	LVDS	$\qquad \qquad -$	CCM_CLK1_N			
CCM CLK1 P	P17	VDD_HIGH_CAP	LVDS	$\overbrace{}$	CCM_CLK1_P			
CCM_PMIC_STBY_REQ	U9	VDD_SNVS_IN	GPIO	ALT0	CCM_PMIC_STBY_REQ	Output		
CSI_DATA00	E ₄	NVCC_CSI	GPIO	ALT5	CSI_DATA00	Input	Keeper	
CSI_DATA01	E ₃	NVCC_CSI	GPIO	ALT5	CSI_DATA01	Input	Keeper	
CSI DATA02	E ₂	NVCC_CSI	GPIO	ALT5	CSI_DATA02	Input	Keeper	
CSI_DATA03	E ₁	NVCC_CSI	GPIO	ALT5	CSI DATA03	Input	Keeper	
CSI_DATA04	D ₄	NVCC_CSI	GPIO	ALT5	CSI_DATA04	Input	Keeper	
CSI_DATA05	D ₃	NVCC_CSI	GPIO	ALT0	CSI_DATA05	Input	Keeper	
CSI_DATA06	D ₂	NVCC_CSI	GPIO	ALT5	CSI_DATA06	Input	Keeper	
CSI_DATA07	D ₁	NVCC_CSI	GPIO	ALT5	CSI_DATA07	Input	Keeper	
CSI_HSYNC	F ₃	NVCC_CSI	GPIO	ALT5	CSI_HSYNC	Input	Keeper	
CSI_MCLK	F ₅	NVCC_CSI	GPIO	ALT5	CSI_MCLK	Input	Keeper	
CSI_PIXCLK	E ₅	NVCC_CSI	GPIO	ALT5	CSI_PIXCLK	Input	Keeper	
CSI_VSYNC	F ₂	NVCC_CSI	GPIO	ALT5	CSI_VSYNC	Input	Keeper	
DRAM_ADDR00	L ₅	NVCC_DRAM	DDR	ALT0	DRAM_ADDR00	Output	100 $k\Omega$ pull-up	
DRAM_ADDR01	H2	NVCC_DRAM	DDR	ALT0	DRAM ADDR01	Output	100 $k\Omega$ pull-up	
DRAM_ADDR02	K ₁	NVCC_DRAM	DDR	ALT0	DRAM_ADDR02	Output	100 k Ω pull-up	
DRAM_ADDR03	M2	NVCC DRAM	DDR	ALT0	DRAM ADDR03	Output	100 k Ω pull-up	
DRAM_ADDR04	K4	NVCC_DRAM	DDR	ALT0	DRAM_ADDR04	Output	100 k Ω pull-up	
DRAM_ADDR05	L1	NVCC_DRAM	DDR	ALT ₀	DRAM ADDR05	Output	100 k Ω pull-up	
DRAM_ADDR06	G ₂	NVCC_DRAM	DDR	ALT0	DRAM ADDR06	Output	100 k Ω pull-up	

Table 90. 14x14 mm Functional Contact Assignments

DRAM ADDR07	H ₄	NVCC DRAM	DDR	ALT0	DRAM ADDR07	Output	100 $k\Omega$ pull-up
DRAM_ADDR08	J4	NVCC_DRAM	DDR	ALT0	DRAM_ADDR08	Output	100 $k\Omega$ pull-up
DRAM ADDR09	L2	NVCC_DRAM	DDR	ALT0	DRAM ADDR09	Output	100 $k\Omega$ pull-up
DRAM_ADDR10	M4	NVCC_DRAM	DDR	ALT0	DRAM_ADDR10	Output	100 $k\Omega$ pull-up
DRAM ADDR11	K ₃	NVCC_DRAM	DDR	ALT0	DRAM_ADDR11	Output	100 $k\Omega$ pull-up
DRAM_ADDR12	L4	NVCC_DRAM	DDR	ALT0	DRAM_ADDR12	Output	100 $k\Omega$ pull-up
DRAM_ADDR13	H3	NVCC_DRAM	DDR	ALT0	DRAM_ADDR13	Output	100 $k\Omega$ pull-up
DRAM ADDR14	G ₁	NVCC_DRAM	DDR	ALT0	DRAM_ADDR14	Output	100 $k\Omega$ pull-up
DRAM_ADDR15	K ₅	NVCC_DRAM	DDR	ALT0	DRAM_ADDR15	Output	100 $k\Omega$ pull-up
DRAM_CAS_B	J2	NVCC DRAM	DDR	ALT0	DRAM CAS B	Output	100 $k\Omega$ pull-up
DRAM_CS0_B	N ₂	NVCC_DRAM	DDR	ALT0	DRAM_CS0_B	Output	100 $k\Omega$ pull-up
DRAM_CS1_B	H ₅	NVCC_DRAM	DDR	ALT0	DRAM_CS1_B	Output	100 $k\Omega$ pull-up
DRAM_DATA00	T ₄	NVCC_DRAM	DDR	ALT0	DRAM_DATA00	Input	100 $k\Omega$ pull-up
DRAM_DATA01	U ₆	NVCC_DRAM	DDR	ALT0	DRAM_DATA01	Input	100 $k\Omega$ pull-up
DRAM_DATA02	T ₆	NVCC DRAM	DDR	ALT0	DRAM DATA02	Input	100 $k\Omega$ pull-up
DRAM DATA03	U7	NVCC_DRAM	DDR	ALT0	DRAM_DATA03	Input	100 kQ pull-up
DRAM DATA04	U8	NVCC_DRAM	DDR	ALT0	DRAM_DATA04	Input	100 $k\Omega$ pull-up
DRAM_DATA05	T ₈	NVCC DRAM	DDR	ALT0	DRAM_DATA05	Input	100 $k\Omega$ pull-up
DRAM_DATA06	T ₅	NVCC_DRAM	DDR	ALT0	DRAM_DATA06	Input	100 $k\Omega$ pull-up
DRAM DATA07	U ₄	NVCC_DRAM	DDR	ALT0	DRAM DATA07	Input	100 $k\Omega$ pull-up
DRAM_DATA08	U2	NVCC_DRAM	DDR	ALT0	DRAM_DATA08	Input	100 $k\Omega$ pull-up

Table 90. 14x14 mm Functional Contact Assignments (continued)

LCD ENABLE	B ₈	NVCC_LCD	GPIO	ALT5	LCD_ENABLE	Input	Keeper
LCD_HSYNC	D ₉	NVCC LCD	GPIO	ALT5	LCD_HSYNC	Input	Keeper
LCD_RESET	E ₉	NVCC_LCD	GPIO	ALT5	LCD_RESET	Input	Keeper
LCD_VSYNC	C ₉	NVCC_LCD	GPIO	ALT5	LCD_VSYNC	Input	Keeper
NAND_ALE	B4	NVCC_NAND	GPIO	ALT5	VDDSOC	Input	Keeper
NAND_CE0_B	C ₅	NVCC NAND	GPIO	ALT5	NAND_CE0_B	Input	Keeper
NAND_CE1_B	B ₅	NVCC_NAND	GPIO	ALT5	NAND_CE1_B	Input	Keeper
NAND_CLE	A4	NVCC_NAND	GPIO	ALT5	NAND_CLE	Input	Keeper
NAND_DATA00	D7	NVCC_NAND	GPIO	ALT5	NAND_DATA00	Input	Keeper
NAND_DATA01	B7	NVCC_NAND	GPIO	ALT5	NAND_DATA01	Input	Keeper
NAND_DATA02	A7	NVCC_NAND	GPIO	ALT5	NAND_DATA02	Input	Keeper
NAND_DATA03	D ₆	NVCC_NAND	GPIO	ALT5	NAND_DATA03	Input	Keeper
NAND_DATA04	C ₆	NVCC_NAND	GPIO	ALT5	NAND_DATA04	Input	Keeper
NAND_DATA05	B ₆	NVCC_NAND	GPIO	ALT5	NAND_DATA05	Input	Keeper
NAND_DATA06	A ₆	NVCC_NAND	GPIO	ALT5	NAND_DATA06	Input	Keeper
NAND_DATA07	A ₅	NVCC_NAND	GPIO	ALT5	NAND_DATA07	Input	Keeper
NAND_DQS	E ₆	NVCC_NAND	GPIO	ALT5	NAND_DQS	Input	Keeper
NAND_RE_B	D ₈	NVCC_NAND	GPIO	ALT5	NAND_RE_B	Input	Keeper
NAND_READY_B	A ₃	NVCC_NAND	GPIO	ALT5	NAND_READY_B	Input	Keeper
NAND_WE_B	C ₈	NVCC_NAND	GPIO	ALT5	NAND_WE_B	Input	Keeper
NAND_WP_B	D ₅	NVCC_NAND	GPIO	ALT5	NAND_WP_B	Input	Keeper
ONOFF	R ₈	VDD_SNVS_IN	GPIO	ALT0	ONOFF	Input	100 $k\Omega$ pull-up
POR_B	P ₈	VDD_SNVS_IN	GPIO	ALT0	POR_B	Input	100 $k\Omega$ pull-up
RTC_XTALI	T11	VDD_SNVS_CAP	ANALOG		RTC_XTALI		
RTC_XTALO	U11	VDD_SNVS_CAP	ANALOG		RTC_XTALO		
SD1_CLK	C ₁	NVCC_SD1	GPIO	ALT5	SD1_CLK	Input	Keeper
SD1_CMD	C ₂	NVCC_SD1	GPIO	ALT5	SD1_CMD	Input	Keeper
SD1_DATA0	B ₃	NVCC_SD1	GPIO	ALT5	SD1_DATA0	Input	Keeper
SD1_DATA1	B ₂	NVCC_SD1	GPIO	ALT5	SD1_DATA1	Input	Keeper
SD1_DATA2	B1	NVCC SD1	GPIO	ALT5	SD1_DATA2	Input	Keeper
SD1_DATA3	A2	NVCC_SD1	GPIO	ALT5	SD1_DATA3	Input	Keeper
SNVS_PMIC_ON_REQ	T ₉	VDD_SNVS_IN	GPIO	ALT0	SNVS_PMIC_ON_REQ	Output	100 $k\Omega$ pull-up

Table 90. 14x14 mm Functional Contact Assignments (continued)

 1 SNVS_TAMPER0 to SNVS_TAMPER9 can be configured as GPIO or tamper detection pin, it is depending on the fuse setting TAMPER_PIN_DISABLE[1:0].

6.1.3 14x14 mm, 0.8 mm pitch, ball map

[Table 91](#page-113-0) shows the 14x14 mm, 0.8 mm pitch ball map for the i.MX 6UltraLite.

Table 91. 14x14 mm, 0.8 mm Pitch, Ball Map

Table 91. 14x14 mm, 0.8 mm Pitch, Ball Map (continued)

6.2 GPIO reset behaviors during reset

[Table 92](#page-115-0) shows the GPIO behaviors during reset.

Table 92. GPIO Behaviors during Reset ¹

Ball Name	Mux Mode	Function	Input/Output	Value
GPIO01 IO03	ALT7	Reserved	Input	100 k Ω pull-down
UART3 TX DATA	ALT7	SJC JTAG ACT	Output	0
LCD DATA00	ALT ₆	SRC BT CFG[0]	Input	100 k Ω pull-down
LCD DATA01	ALT ₆	SRC BT CFG[1]	Input	100 k Ω pull-down
LCD DATA02	ALT ₆	SRC_BT_CFG[2]	Input	100 k Ω pull-down
LCD DATA03	ALT ₆	SRC BT CFG[3]	Input	100 k Ω pull-down
LCD DATA04	ALT ₆	SRC BT CFG[4]	Input	100 k Ω pull-down

¹ Others are same as value in the column "Out of Reset Condition" of [Table 90](#page-105-0).

[Revisio](#page-26-0)n history

[7 Revision history](#page-29-0)

[Table 93](#page-117-0) [provides a revis](#page-63-0)[ion](#page-89-0) history for this data sheet.

